軍商兩用貨品及技術出口管制清單及一般軍用貨品清單
新、舊版修正對照與翻譯

編列說明

1. 軍商兩用貨品及技術出口管制清單列入第一項，一般軍用貨品清單列入第二項。
2. 本對照表列出下列情況：
   a. 中文有增/刪語詞，原意有所變動者；
   b. 舊版無、新版新增之內容；
   c. 舊版有、新版刪除之內容；
3. 本對照表未列出下列情況，但已於檔案中進行修正，與現行公布英文版本一致：
   a. 標點符號變動、專有名詞單引號或雙引號變動、CAS 編號前加註 CAS 字樣者；
   b. 英文編輯改變，未改變原有內容意義者；
   c. 排版方式變更，未改變原有內容意義者；
   d. 既有版本的錯字與誤植。
4. 為符合國際文體指南(2015年版)，英文版本以逗號分隔整數與小數，以空間分隔表明千位整數。

目錄

第一項：軍商兩用貨品及技術出口管制清單修正對照表(黃色為修正差異)

修正條目	現行內容	擬修正/新增內容	現行內容英譯	擬修正/新增內容英譯
AIP	新增	無空氣推進系統	--	Air Independent Propulsion
專用術語定義				
“Charge multiplication ”	新增	〝電荷倍增〞（第6類)是指電子影像放大的一種形式，其定義為由於碰撞電離增益過程而產生電荷載子。〝電荷倍增〞感測器可以採用影像增強管、固態偵測器或〝焦平面陣列〞的形式。	--	"Charge multiplication" (6) means a form of electronic image amplification defined as the generation of charge carriers as a result of an impact ionisation gain process. "Charge multiplication" sensors may take the form of an image intensifier tube, solid state detector or "focal plane array"
"High outputdiesel engines"	新增	〝高功率柴油引擎〞（第9類）若額定轉速為2,300 r.p.m.或以上，而轉速在2,300 r.p.m.時，其特定之制動平均有效壓力為1.8 MPa或以上之柴油發動機。	--	"High output diesel engines" (9) means diesel engines with a specified brake mean effective pressure of 1,8 MPa or more at a speed of 2 300 r.p.m., provided the rated speed is 2 300 r.p.m. or more.
“Insulation”	〝絕緣〞(第9類)係指應用於火箭推進器之零件，例如殼體、噴嘴、入口、殼體罩，以及包括凝固或半凝固之複合橡膠片，包含絕緣或耐熱材料，其亦可能併於釋放應力之防護罩或襟翼中。	刪除	"Insulation" (9) is applied to the components of a rocket motor, i.e. the case, nozzle, inlets, case closures, and includes cured or semi-cured compounded rubber sheet stock containing an insulating or refractory material. It may also be incorporated as stress relief boots or flaps.	--
0B004.a.3	新增	3. 複合電解暨催化交換（CECE）廠；	--	3.Combined Electrolysis and Catalytic Exchange (CECE) plants;
0B004.a.4	新增	4. 複合工業重整暨催化交換（CIRCE）廠；	--	4.Combined Industrial Reforming and Catalytic Exchange (CIRCE) plants;
0B004.a.5	新增	5. 雙溫氫—水交換（BHW）廠；	--	5.Bithermal Hydrogen-Water exchange (BHW) plants;

修正條目	現行內容	擬修正/新增內容	現行內容英譯	擬修正/新增內容英譯
0B004.b.2	2.單級式，低壓(即：0.2 MPa)之離心風機或壓縮機，用於為硫化 氫(H2S)氣體循環(即氣體含有重量比超過70%之 H2S)，其在操作壓力大於或等於 1.8 MPa 吸力時，氣體流通量等於或大於 56 m^3/s，且具有使用溼式 H2S 之密封設計。	2. 單級式，低壓(即：0.2 MPa)之離心風機或壓縮機，用於為硫化氫(H2S)氣體循環(即氣體含有重量比超過70%之 H2S)，其在操作壓力大於或等於1.8 MPa 吸力時，氣體流通量等於或大於5 m^3/s，且具有使用溼式 H2S 之密封設計。	2.Single stage, low head (i.e., 0,2 MPa) centrifugal blowers or compressors for hydrogen sulphide gas circulation (i.e., gas containing more than 70 % by weight hydrogen sulphide, H2S) with a throughput capacity greater than or equal to 56 m3/s when operating at pressures greater than or equal to 1,8 MPa suction and having seals designed for wet H2S service;	2.Single stage, low head (i.e., 0,2 MPa) centrifugal blowers or compressors for hydrogen sulphide gas circulation (i.e., gas containing more than 70 % by weight hydrogen sulphide, H2S) with a throughput capacity greater than or equal to 5 m^3/s when operating at pressures greater than or equal to 1,8 MPa suction and having seals designed for wet H2S service;
0B004.b.3	3.氨-氫交換塔，其高度大於或等於 35 m，直徑介於 1.5 m 至 2.5m，可在壓力大於 15 MPa 下操作；	3. 氨-氫交換塔，其高度大於或等於 35 m，直徑大於或等於1.5 m，可在壓力大於 15 MPa 下操作；	3.Ammonia-hydrogen exchange towers greater than or equal to 35 m in height with diameters of 1,5 m to 2,5 m capable of operating at pressures greater than 15 MPa;	3.Ammonia-hydrogen exchange towers greater than or equal to 35 m in height with diameters of 1,5 m or greater capable of operating at pressures greater than 15 MPa;
0B004.b.6	6.在氘濃度重量比等於或大於 90 % 時，可進行線上氫/氘比例分析之紅外線吸收分析儀；	6. 刪除;	6.Infrared absorption analysers capable of on-linehydrogen/deuterium ratio analysis where deuterium concentrations are equal to or greater than 90 %;	6.Not used;
0B004.b.8	8.完整的重水升級系統或圓柱，用於將重水濃度提升至反應器等級之氘濃度；	8.完整的重水升級系統，或直徑大於或等於0.1 m 的圓柱，用於將重水濃度提升至反應器等級之氘濃度；	8.Complete heavy water upgrade systems, or columns therefor, for the upgrade of heavy water to eactor-grade deuterium concentration;	8.Complete heavy water finishing units, upgrade systems, or columns with diameters of 0,1 m or greater therefor, for the upgrade of heavy water to reactor-grade deuterium concentration;
0B004.b.10	新增	10.專為氫同位素交換設計或製造的完整的塔或柱，且具有下列所有特性： 1.採用散裝或結構化防潮鉑催化劑進行填充； 2.採用碳鋼或不銹鋼製成； 3.可在0.1至4MPa 的壓力範圍內運轉；和	--	10.Complete columns or towers specially designed or prepared for hydrogen isotope exchange having all of the following: 1.Packed with random or structured wet-proofed platinised catalysts; 2.Constructed of carbon steel or stainless steel; 3.Capable of operating with pressure in the range of 0,1 to 4 MPa; and 4.Capable of operating at temperatures

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		4.能夠在 293 K (20 °C) 至 473 K (200 °C) 的溫度範圍內運作。		in the range of 293 K (20 °C) to 473 K (200 °C).
1A003 註解	註解：1A003 不管制以銅塗佈或積層，且設計為生產電子印刷電路板之製品。	註解：1A003不管制以銅塗佈或積層，且設計為〝生產〞電子印刷電路板之製品。	1A003 does not control manufactures when coated or laminated with copper and designed for the production of electronic printed circuit boards.	1A003 does not control manufactures when coated or laminated with copper and designed for the "production" of electronic printed circuit boards.
1A202	除 1A002 所述以外之管狀複合結構，且具下列所有特性： 說明：參照 9A010 及 9A110。 a.內徑介於 75 mm 至 400 mm 之間；及 b.以 1C010.a.或 b.或 1C210.a.所述之任一〝纖維或絲狀材料〞製造，或以 1C210.c.所述之碳預浸體材料製造。	除 1A002 所述以外之薄壁管狀複合結構，且具下列所有特性： 說明：參照 9A010 及 9A110。 a.內徑介於 75 mm 至 650 mm 之間；及 b. 厚度為 12 mm 或以下；及 c.以 1C010.a.或 b.或 1C210.a.所述之任一〝纖維或絲狀材料〞製造，或以 1C210.c.所述之碳預浸體材料製造。	Composite structures, other than those specified in 1A002, in the form of tubes and having both of the following characteristics: N.B. SEE ALSO 9A010 AND 9A110. a.An inside diameter of between 75 mm and 400 mm; and b.Made with any of the "fibrous or filamentary materials" specified in 1C010.a. or b. or 1C210.a. or with carbon prepreg materials specified in 1C210.c.	Composite structures, other than those specified in 1A002, in the form of thin-walled tubes and having all of the following characteristics: N.B. SEE ALSO 9A010 AND 9A110. a.An inside diameter of between 75 mm and 650 mm; b.A thickness of 12 mm or less; and c.Made with any of the "fibrous or filamentary materials" specified in 1C010.a. or b. or 1C210.a. or with carbon prepreg materials specified in 1C210.c.
1A225	為促進氫與水間之氫同位素交換反應而特別設計或製備之鍍鉑催化劑，此交換反應是為從重水中回收氚或為製造重水。	為促進氫與水間之氫同位素交換反應而特別設計或製備之防潮鍍鉑催化劑，此交換反應是為從水中回收氚或為製造或升級重水。	Platinized catalysts specially designed or prepared for promoting the hydrogen isotope exchange reaction between hydrogen and water for the recovery of tritium from heavy water or for the production of heavy water.	Wet-proofed platinized catalysts specially designed or prepared for promoting the hydrogen isotope exchange reaction between hydrogen and water for the recovery of tritium from water or for the production or upgrading of heavy water.
1B001	特別設計用於生產或檢測 1A002 所述〝複合材料〞結構或積層板，或 1C010 所述〝纖維狀或絲狀材料〞之設備，及其特別設計之零件及配件：	特別設計用於〝生產〞〝複合材料〞結構或積層板，或〝纖維狀或絲狀材料〞之設備，及其特別設計之零件及配件：	Equipment for the production or inspection of "composite" structures or laminates specified in 1A002 or "fibrous or filamentary materials" specified in 1C010, as follows, and specially designed components and accessories therefor:	Equipment designed for the "production" of "composite" structures or laminates or "fibrous or filamentary materials", as follows, and specially designed components and accessories therefor:

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1B001.d	d.為生產強化纖維而特別設計或改裝之設備，如下：	d. 為〝生產〞1C010所述〝纖維狀或絲狀材料〞而特別設計或改裝之設備，如下：	d.Equipment specially designed or adapted for the production of reinforcement fibres, as follows:	d.Equipment specially designed or modified for the "production" of "fibrous or filamentary materials" specified by 1C010, as follows:
1B001.e	e.以熱融法生產 1C010.e.所述之預浸體的設備；	e. 特別設計或改裝以〝熱融法〞〝生產〞預浸體的設備；.	e.Equipment for producing prepregs specified in 1C010.e. by the hot melt method;	e.Equipment specially designed or modified for the production of prepregs by the 'hot melt method';
1B001.e 技術註解	新增	就1B001.e.的目的，〝熱融法〞是指通過施加壓力和熱量，將預先層壓在載體基材（如薄膜或紙張）上的樹脂浸漬到〝纖維或絲狀材料〞中的過程。	--	For the purposes of 1B001.e., the 'hot melt method' is the process of applying pressure and heat to impregnate "fibrous or filamentary materials" with resin that has been pre-laminated onto a carrier substrate, such as film or paper.
1B228	具下列所有特性之氫-低溫蒸餾塔： a.於內部溫度為 35 K(-238 °C)或以下操作而設計者； b.為於內部壓力 0.5 MPa 至 5 MPa 條件下操作而設計者； c.由下列任一材料建構而成： 1. 國際汽車工程師協會(SAE)之 300 系列不銹鋼，具低含硫量，且其沃斯田(austenitic)美國材料試驗學會(ASTM)(或等效標準)之晶粒大小為 5 或以上者；或 2.兼具低溫且與氫氣(H2)相容之同等材料；及 d.內徑 30 cm 或以上，且'有效長度'為 4 m 或以上。	具下列所有特性之氫-低溫蒸餾塔： a.為於內部溫度 15 K(-258 °C) 至35 K(-238 °C) 範圍內操作而設計者； b.為於內部壓力 0.1 MPa 至 1 MPa 條件下操作而設計者； c.由下列任一材料建構而成： 1. 奧氏體不銹鋼；或 2. 在15 K（-258°C）至35 K（-238°C）範圍內兼具低溫且與氫氣(H2)相容之同等材料；及 d.內徑 30 cm 或以上，且'有效長度'為 4 m 或以上。	Hydrogen-cryogenic distillation columns having all of the following characteristics: a.Designed for operation with internal temperatures of 35 K (– 238 °C) or less; b.Designed for operation at an internal pressure of 0,5 to 5 MPa; c.Constructed of either: 1.Stainless steel of the Society of Automotive Engineers International (SAE) 300 series with low sulphur content and with an austenitic ASTM (or equivalent standard) grain size number of 5 or greater; or 2.Equivalent materials which are both	Hydrogen-cryogenic distillation columns having all of the following characteristics: a.Designed for operation with internal temperatures in the range of 15 K (-258 °C) to 35 K (-238 °C); b.Designed for operation at internal pressures in the range of 0,1 MPa to 1 MPa; c.Constructed of either: 1.Austenitic stainless steel; or 2.Equivalent materials which are both cryogenic and hydrogen (H2)-compatible between 15 K (-258 °C) and 35 K(-238 °C); and

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	技術註解： 在 1B228 中之'有效長度'，指填充式蒸餾塔之填充材料活性高度，或板式蒸餾塔內部接觸器板之活性高度。	技術註解1： 在 1B228 中之'有效長度'，指填充式蒸餾塔之填充材料活性高度，或板式蒸餾塔內部接觸器板之活性高度。	cryogenic and hydrogen (H2)-compatible; and d.With internal diameters of 30 cm or greater and 'effective lengths' of 4 m or greater. Technical Note: In 1B228 'effective length' means the active height of packing material in a packed-type column, or the active height of internal contactor plates in a plate-type column.	d.With internal diameters of 30 cm or greater and 'effective lengths' of 4 m or greater. Technical Note 1: In 1B228 'effective length' means the active height of packing material in a packed-type column, or the active height of internal contactor plates in a plate-type column.
1B228 技術註解 2	新增	技術註解2： 同等材料可能包括但不限於以下材料： a. 鋁， b. 鋁合金， c. 銅合金 d. 鎳合金，及 e. 鈦合金。	--	Technical Note 2: Equivalent materials could include, but are not limited to the following materials: a.aluminium, b.aluminium alloys, c.copper alloys, d.nickel alloys, and e.titanium alloys.
1C011.e	新增	e. 五氟化碘(CAS 7783-66-6).	--	e.Iodine pentafluoride (CAS 7783-66-6).
1C350.90	新增	90. 二丙胺(CAS 142-84-7).	--	90.Dipropylamine (CAS 142-84-7).

修正條目	現行內容	擬修正/新增內容	現行內容英譯	擬修正/新增內容英譯
1C351.d.20-24	新增	20. 布雷維毒素； 21. 剛毛毒素； 22. 結節毒素； 23. 巴利毒素； 24. 新沙門氏毒素（NEO）。	--	20. Brevetoxins; 21. Gonyautoxins; 22. Nodularins; 23. Palytoxin; 24. Neosaxitoxin (NEO).
2B116.a 技術註解	新增	在 2B116. a. 中，〝包含數位控制器之振動測試系統〞是指其功能部分或全部由儲存的、數位編碼的電訊號自動控制的系統。	--	Technical Note: In 2B116.a., 'vibration test systems incorporating a digital controller' are those systems, the functions of which are, partly or entirely, automatically controlled by stored and digitally coded electrical signals.
2B116.b .c, .d	b. 與特別設計之振動測試軟體結合之數位控制器，具有5 kHz 以上之'即時控制頻寬'，且設計與2B116.a.所述之~~振動測試~~系統共同使用； c. 具有或不具有相關放大器之振動推力器(搖動單元)，能施加等於或大於50 kN 之力，此力係於'無遮平檯'測量，且能使用於2B116.a.所述之~~振動測試~~系統； d. 經設計為使某一系統內之複合式搖動單元結合之測試物件支撐結構及電子單元，能提供等於或大於50 kN 之有效混合力，此力係於'無遮平檯'測量，且能使用於2B116.a.所述之~~振動~~系統。	b. 與特別設計之振動測試軟體結合之數位控制器，具有5 kHz 以上之'即時控制頻寬'，且設計與2B116.a.所述之系統共同使用； c. 具有或不具有相關放大器之振動推力器(搖動單元)，能施加等於或大於50 kN 之力，此力係於'無遮平檯'測量，且能使用於2B116.a.所述之系統； d. 經設計為使某一系統內之複合式搖動單元結合之測試物件支撐結構及電子單元，能提供等於或大於50 kN 之有效混合力，此力係於'無遮平檯'測量，且能使用於2B116.a.所述之系統。	b.Digital controllers, combined with specially designed vibration test software, with a 'real-time control bandwidth' greater than 5 kHz designed for use with ~~vibration test~~ systems specified in 2B116.a.; c.Vibration thrusters (shaker units), with or without associated amplifiers, capable of imparting a force equal to or greater than 50 kN, measured 'bare table', and usable in ~~vibration test~~ systems specified in 2B116.a.; d.Test piece support structures and electronic units designed to combine multiple shaker units in a system capable of providing an effective combined force equal to or greater than 50 kN, measured 'bare table', and usable in ~~vibration~~ systems specified in 2B116.a.	b.Digital controllers, combined with specially designed vibration test software, with a 'real-time control bandwidth' greater than 5 kHz designed for use with systems specified in 2B116.a.; c. Vibration thrusters (shaker units), with or without associated amplifiers, capable of imparting a force equal to or greater than 50 kN, measured 'bare table', and usable in systems specified in 2B116.a.; d.Test piece support structures and electronic units designed to combine multiple shaker units in a system capable of providing an effective combined force equal to or greater than 50 kN, measured 'bare table', and usable in systems specified in 2B116.a.

修正條目	現行內容	擬修正/新增內容	現行內容英譯	擬修正/新增內容英譯
2B351.a	a.為連續操作而設計，且可用於偵測濃度小於 0.3 mg/m3 之化學戰劑或 1C350 所述之化學品；或	a. 為連續操作而設計，且可用於偵測〝最低檢出極限〞小於 0.3 mg/m3 之化學戰劑或 1C350 所述之化學品；或	a.Designed for continuous operation and usable for the detection of chemical warfare agents or chemicals specified in 1C350, at concentrations of less than 0,3 mg/m3; or	a.Designed for continuous operation and usable for the detection of chemical warfare agents or chemicals specified in 1C350 with a 'minimum detection limit' of less than 0,3 mg/m3; or
2B351.a 技術註解	新增	技術註解： 有毒氣體監測儀或監測系統的〝最低檢出極限〞是指在測量空白樣本時，能產生大於該監測儀或監測系統信號三倍標準偏差的分析物濃度。 在有毒氣體監測器或監測系統中，若設有死區或程式化零點抑制，'最低檢出極限'是指能產生讀數的最低氣體濃度。	--	Technical Note: The 'minimum detection limit' of toxic gas monitors or moni toring systems is the lowest detectable concentration of the analyte required to produce a signal greater than three times the standard deviation of the toxic gas monitor's or monitoring system's signal when measuring a blank sample. In the case of toxic gas monitors or monitoring systems having a deadband or programmed zero suppression, the 'minimum detection limit' is the lowest detectable concentration required to produce a reading.
2B910	新增	2B910 設計用於生產金屬或金屬合金零件的增材製造設備，以及為其〝特別設計〞的〝零件〞，具有以下所有特性： a.至少擁有以下任一凝固源： 1."雷射"； 2.電子束；或 3.電弧； b.具備以下任一管控製程氣體： 1.惰性氣體；或 2.真空（等於或小於100Pa）； c.以'同軸配置'或'旁軸配置'的形式存在的'製程監測'設備，具有以下任一特性： 1.峰值響應波長範圍超過380 nm但	--	2B910 Additive manufacturing equipment, designed to produce metal or metal alloy components, having all of the following, and "specially designed" "components" therefor. a. Having at least one of the following consolidation sources: a.1. "Laser" ; a.2. Electron beam; or a.3. Electric arc; b. Having a controlled process atmosphere of any of the following: b.1. Inert gas; or

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		不超過14,000 nm的成像相機； 2.設計用於測量高於 1,273.15K (1,000 °C) 溫度的高溫計；或 3.峰值響應波長範圍超過380 nm 但不超過3000 nm 的輻射計或光譜儀；及 d.封閉迴路控制系統，根據 2B010.c 中規定的設計用於'製程監測'設備的回應，在製造過程中修改凝固源參數、構建路徑或設備設定。 技術註解： 就 2B910 而言： 1.'製程監測'，也稱為原位製程監控，涉及增材製造過程的觀察和測量，包括熔池的電磁或熱排放。 2.'同軸配置'，也稱為同軸或內嵌配置，涉及安裝在"雷射"凝固源共享的光路中的一個或多個感測器。 3.'近軸配置'涉及實體安裝到或整合到 "雷射"、電子束或電弧凝固源組件上的一個或多個感測器。 4. 對於'同軸配置'和'近軸配置'，感測器的視場固定到凝固源的移動參考框架中，並在構建過程中隨著凝固源的掃描軌跡移動。		b.2. Vacuum (equal to or less than 100 Pa); c. Having any of the following 'in-process monitoring' equipment in a 'co-axial configuration' or 'paraxial configuration': c.1. Imaging camera with a peak response in the wavelength range exceeding 380 nm but not exceeding 14,000 nm; c.2. Pyrometer designed to measure temperatures greater than 1,273.15K (1,000 °C); or c.3. Radiometer or spectrometer with a peak response in the wavelength range exceeding 380 nm but not exceeding 3,000 nm; and d. A closed loop control system designed to modify the consolidation source parameters, build path, or equipment settings during the build cycle in response to feedback from 'in-process monitoring' equipment . Technical Notes: For the purposes of 2B910: 1. 'In-process monitoring', also known as in-situ process monitoring, pertains to the observation and measurement of the additive manufacturing process including electromagnetic, or thermal, emissions from the melt pool. 2. 'Co-axial configuration', also known as on-axis or inline configuration, pertains to one or more sensors that are

修正條目	現行內容	擬修正/新增內容	現行內容英譯	擬修正/新增內容英譯
				mounted in an optical path shared by the “laser” consolidation source. 3. 'Paraxial configuration' pertains to one or more sensors that are physically mounted onto or integrated into the “laser” , electron beam, or electric arc consolidation source component. 4. For both 'co-axial configuration' and 'paraxial configuration', the field of view of the sensor(s) is fixed to the moving reference frame of the consolidation source and moves in the same scan trajectories of the consolidation source throughout the build process.
2D910	新增	2D910 專門為〝開發〞或〝生產〞2B910中列明的設備而特別設計或修改的〝軟體〞。	--	"Software", not specified elsewhere, " specially designed " or modified for the "development" or "production" of equipment specified in 2B910.
2E903	新增	2E903 其他地方未指定的用於〝開發〞或〝生產〞具有以下所有'塗層系統'的〝技術〞： a. 設計用於保護1C007規定的陶瓷〝基體〞〝複合〞材料免受腐蝕；及 b. 設計用於工作溫度超過1,373.15 K (1,100 °C)。 技術註解： 就2E903而言，'塗層系統'由沉積在基材上的一層或多層（例如，黏合層、中間層、面塗層）材料所組成。	--	"Technology" , not specified elsewhere, for the "development" or "production" of `coating systems' having all of the following: a. Designed to protect ceramic " matrix " " composite " materials specified by 1C007 from corrosion; and b. Designed to operate at temperatures exceeding 1,373.15 K (1,100 °C). Technical Note: For the purposes of 2E903, 'coating systems' consist of one or more layers (e.g., bond, interlayer, top coat) of material deposited on the substrate.

修正條目	現行內容	擬修正/新增內容	現行內容英譯	擬修正/新增內容英譯
2E910	新增	2E910 未在其他地方指定的專門為〝開發〞或〝生產〞 2B910 中列明的設備而〝特別設計〞或修改的〝技術〞。	--	"Technology", not specified elsewhere, " specially designed " or modified for the "development" or "production" of equipment specified in ECCN 2B910.
3A 註解 1	註解 1：3A001 或 3A002 中除 3A001.a.3.至 3A001.a.10.、3A001.a.12.至 3A001.a.14,或 3A001.b.12.所述以外之設備與零件管制狀況，專為其他設備所設計或具有與其他設備相同功能特徵者，由 其他設備之管制狀況所決定。	中文未變更	Note 1: The control status of equipment and components described in 3A001 or 3A002, other than those described in 3A001.a.3. to 3A001.a.10., ~~or~~ 3A001.a.12. to 3A001.a.14., or 3A001.b.12., which are specially designed for or which have the same functional characteristics as other equipment is determined by the control status of the other equipment.	Note 1: The control status of equipment and components described in 3A001 or 3A002, other than those described in 3A001.a.3. to 3A001.a.10., 3A001.a.12. to 3A001.a.14., or 3A001.b.12, which are specially designed for or which have the same functional characteristics as other equipment is determined by the control status of the other equipment.
3A001.b.7.a-b	a.設計用於延伸〝訊號分析儀〞頻率範圍超過 90 GHz； b.設計用於延伸訊號產生器操作範圍如下： 1.超過 90 GHz； 2.輸出功率大於 100 mW(20dBm)，頻率範圍超過 43.5 GHz 但未超過 90 GHz；	a. 設計用於延伸〝訊號分析儀〞頻率範圍超過 110 GHz； b. 設計用於延伸訊號產生器操作範圍如下： 1. 超過 110 GHz； 2. 輸出功率大於 100 mW(20dBm)，頻率範圍超過 43.5 GHz 但未超過 110 GHz；	a.Designed to extend the frequency range of "signal analysers" beyond 90 GHz; b.Designed to extend the operating range of signal generators as follows: 1.Beyond 90 GHz; 2.To an output power greater than 100 mW (20 dBm) anywhere within the frequency range exceeding 43,5 GHz but not exceeding 90 GHz;	a.Designed to extend the frequency range of "signal analysers" beyond 110 GHz; b.Designed to extend the operating range of signal generators as follows: 1.Beyond 110 GHz; 2.To an output power greater than 100 mW (20 dBm) anywhere within the frequency range exceeding 43,5 GHz but not exceeding 110 GHz;
3A001.b.7.c.2	2.輸出功率大於 31.62 mW(15dBm)，頻率範圍超過 43.5 GHz 但未超過 90 GHz；	2.輸出功率大於 100 mW (20 dBm)，頻率範圍超過 43.5 GHz 但未超過 110 GHz；	2.To an output power greater than 31,62 mW (15 dBm) anywhere within the frequency range exceeding 43,5 GHz but not exceeding 90 GHz;	2.To an output power greater than 100 mW (20 dBm) anywhere within the frequency range exceeding 43,5 GHz but not exceeding 110 GHz;
3A001.b.7.c.3	3.輸出功率大於 1 mW(0dBm)，頻率範圍超過 90 GHz 但未超過110 GHz；或	3.刪除	3.To an output power greater than 1 mW (0 dBm) anywhere within the frequency range exceeding 90 GHz but not exceeding 110 GHz; or	3.Not used;
3A001.b.9. 技術註解	就 3A001.b.9.目的： 1.計算 3A001.b.9.b.所述之體積，如	1. 就3A001.b.9.a.目的，所述之'開機時間'指的是完全關機到完全	For the purposes of 3A001.b.9.: 1.To calculate the volume in 3A001.b.9.b., the following example	1.For the purposes of 3A001.b.9.a. the 'turn-on time' refers to the time from fully-off to fully operational, i.e., it

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	下例所示：最大評定功率20W之管制體積為20 W× 10 cm3/W＝200 cm3。 2. 3A001.b.9.a.所述之'開機時間'指的是完全關機到完全運作狀態之時間；亦即包括微波功率模組(MPM)熱機時間。	運作狀態之時間；亦即包括微波功率模組(MPM)熱機時間。 2. 就3A001.b.9.b.目的，計算3A001.b.9.b.所述之體積，如下例所示：最大評定功率20W之管制體積為20 W×10 cm^3/W＝200 cm^3。	is provided: for a maximum rated power of 20 W, the volume would be: 20 W × 10 cm3/W = 200 cm3. 2.The' turn-on time' in 3A001.b.9.a. refers to the time from fully-off to fully operational, i.e., it includes the warm-up time of the MPM.	includes the warm-up time of the MPM. 2.For the purposes of 3A001.b.9.b., the following example is provided to calculate the volume: for a maximum rated power of 20 W, the volume would be: 20 W × 10 cm^3/W = 200 cm^3.
3A002.c.2-4	2.〝訊號分析儀〞具有平均顯示雜訊位準(DNAL)在任何地方低於(優於)-150 dBm/Hz，其頻率超過43.5 GHz但不超過90 GHz； 3.〝訊號分析儀〞頻率超過90 GHz； 4.〝訊號分析儀〞具有下列所有特性： a.'即時頻寬'超過170 MHz；及 b.具下列任一特性： 1.具100%的發現率，於間隙或訊號的開窗效應持續時間為15 μs或以下，全振幅降低小於3 dB； 2.具有'頻率遮罩觸發'功能，其100%觸發(捕獲)訊號機率之持續時間為15 μs或以下；	2.〝訊號分析儀〞具有平均顯示雜訊位準(DNAL)在任何地方低於(優於)-160 dBm/Hz，其頻率超過43.5 GHz但不超過110 GHz； 3.〝訊號分析儀〞頻率超過110 GHz； 4.〝訊號分析儀〞具有下列所有特性： a.'即時頻寬'超過520 MHz；及 b.具下列任一特性： 1.具100%的發現率，於間隙或訊號的開窗效應持續時間為8 μs或以下，全振幅降低小於3 dB； 2.具有'頻率遮罩觸發'功能，其100%觸發(捕獲)訊號機率之持續時間為8 μs或以下；	2."Signal analysers" having a Displayed Average Noise Level (DANL) less (better) than -150 dBm/Hz anywhere within the frequency range exceeding 43,5 GHz but not exceeding 90 GHz; 3."Signal analysers" having a frequency exceeding 90 GHz; 4."Signal analysers" having all of the following: a.'Real-time bandwidth' exceeding 170 MHz; and b. Having any of the following: 1.100 % probability of discovery with less than a 3 dB reduction from full amplitude due to gaps or windowing effects of signals having a duration of 15 μs or less; or 2.A 'frequency mask trigger' function with 100 % probability of trigger (capture) for signals having a duration of 15 μs or less;	2."Signal analysers" having a Displayed Average Noise Level (DANL) less (better) than -160 dBm/Hz anywhere within the frequency range exceeding 43,5 GHz but not exceeding 110 GHz; 3."Signal analysers" having a frequency exceeding 110 GHz; 4."Signal analysers" having all of the following: a.'Real-time bandwidth' exceeding 520 MHz; and b.Having any of the following: 1.100 % probability of discovery with less than a 3 dB reduction from full amplitude due to gaps or windowing effects of signals having a duration of 8 μs or less; or 2.A 'frequency mask trigger' function with 100 % prob ability of trigger (capture) for signals having a duration of 8 μs or less;
3A002.d.1 技術註解	新增	技術註解： 就3A002.d.1.a.目的，'脈衝持續時間'定義為由脈衝波之前緣達50%	--	For the purposes of 3A002.d.1.a, 'pulse duration' is defined as the time interval from the point on the leading edge that

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		之一點，至脈衝波後緣達50%之一點兩者其時間間隔。		is 50 % of the pulse amplitude to the point on the trailing edge that is 50 % of the pulse amplitude.
3A002.d.2-6	2.任何地方輸出功率超過 100 mW(20 dBm)，其頻率超過 43.5 GHz 但不超過 90 GHz； 3.g.在頻率超過 75 GHz，但不超過 90 GHz 的條件下，頻率變化超過 5.0 GHz 時之切換時間小於 100 μs； 4.a.在頻率超過 3.2 GHz 但不超過 90 GHz，10 Hz≤F≤10 kHz 範圍之中，少於(優於) -(126+20 log10F-20 log10f)；或 4.b.在頻率超過 3.2 GHz 但不超過 90 GHz，10 kHz＜F≤100 kHz 範圍之中，少於(優於) -(206-20 log10f)；或 5.d. 在頻率範圍超過 75 GHz 但不超過 90 GHz 情況下，超過 5.0 GHz 者；或 6.最大頻率超過 90 GHz；	2.任何地方輸出功率超過 100 mW(20 dBm)，其頻率超過 43.5 GHz 但不超過 110 GHz； 3.g.在頻率超過 75 GHz，但不超過 110 GHz 的條件下，頻率變化超過 5.0 GHz 時之切換時間小於 100 μs； 4.a.在頻率超過 3.2 GHz 但不超過 110 GHz，10 Hz≤F≤10 kHz 範圍之中，少於(優於) -(126+20 log10F-20 log10f)；或 4.b.在頻率超過 3.2 GHz 但不超過 110 GHz，10 kHz＜F≤100 kHz 範圍之中，少於(優於) -(206-20 log10f)；或 5.d. 在頻率範圍超過 75 GHz 但不超過 110 GHz 情況下，超過 5.0 GHz 者；或 6.最大頻率超過 110 GHz；	2.An output power exceeding 100 mW (20 dBm) anywhere within the frequency range exceeding 43,5 GHz but not exceeding 90 GHz; 3.g.Less than 100 μs for any frequency change exceeding 5,0 GHz within the frequency range exceeding 75 GHz but not exceeding 90 GHz; 4.a.Less (better) than -(126 + 20log10F - 20log10f) anywhere within the range of 10 Hz ≤ F ≤ 10 kHz anywhere within the frequency range exceeding 3,2 GHz but not exceeding 90 GHz; or 4.b.Less (better) than -(206-20log10f) anywhere within the range of 10 kHz< F≤ 100 kHz anywhere within the frequency range exceeding 3,2 GHz but not exceeding 90 GHz; or 5.d.Exceeding 5,0 GHz within the frequency range exceeding 75 GHz but not exceeding 90 GHz; or 6.A maximum frequency exceeding 90 GHz;	2.An output power exceeding 100 mW (20 dBm) anywhere within the frequency range exceeding 43,5 GHz but not exceeding 110 GHz; 3.g.Less than 100 μs for any frequency change exceeding 5,0 GHz within the frequency range exceeding 75 GHz but not exceeding 110 GHz; 4.a.Less (better) than -(126 + 20log10F - 20log10f) anywhere within the range of 10 Hz ≤ F ≤ 10 kHz anywhere within the frequency range exceeding 3,2 GHz but not exceeding 110 GHz; or 4.b.Less (better) than -(206 - 20log10f) anywhere within the range of 10 kHz< F≤ 100 kHz anywhere within the frequency range exceeding 3,2 GHz but not exceeding 110 GHz; 5.d.Exceeding 5,0 GHz within the frequency range exceeding 75 GHz but not exceeding 110 GHz; or 6.A maximum frequency exceeding 110 GHz;
3A002.d. 技術註解	技術註解： 1.就 3A002.d.目的，任意波形及函數產生器之最大頻率計算，為以秒計算之取樣率除以係數 2.5。	技術註解： 就 3A002.d.目的，任意波形及函數產生器之最大頻率計算，為以秒計算之取樣率除以係數 2.5。	Technical Notes : 1.For the purposes of 3A002.d., the maximum frequency of an arbitrary waveform or function generator is calculated by dividing the sample rate, in samples/second, by a factor of	Technical Note: For the purposes of 3A002.d., the maximum output frequency of an arbitrary waveform or function generator is calculated by dividing the sample rate, in samples/second, by a

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	2. 就 3A002.d.1.a.目的，'脈衝持續時間'定義為由脈衝波之前緣達 50%之一點，至脈衝波後緣達 50%之一點兩者其時間間隔。		2,5. 2.For the purposes of 3A002.d.1.a, 'pulse duration' is defined as the time interval from the point on the leading edge that is 50 % of the pulse amplitude to the point on the trailing edge that is 50 % of the pulse amplitude.	factor of 2,5.
3A002.e.1	1.輸出功率超過 31.62 mW (15 dBm)之任一處其最大操作頻率超過 43.5 GHz 但未超過 90 GHz；	1. 輸出功率超過100 mW (20 dBm)之任一處其最大操作頻率超過43.5 GHz 但未超過110 GHz；	1.An output power exceeding 31,62 mW (15 dBm) anywhere within the operating frequency range exceeding 43,5 GHz but not exceeding 90 GHz;	1.An output power exceeding 100 mW (20 dBm) anywhere within the operating frequency range exceeding 43,5 GHz but not exceeding 110 GHz;
3A002.e.2	2.輸出功率超過 1 mW (0 dBm)之任一處其最大操作頻率超過 90 GHz 但未超過 110 GHz；	2.刪除；	2.An output power exceeding 1 mW (0 dBm) anywhere within the operating frequency range exceeding 90 GHz but not exceeding 110 GHz;	2.Not used;
3A901	新增	3A901 3A001 未指定的電子產品，如下： a.互補金屬氧化物半導體 (CMOS)積體電路，未在 3A001.a.2 中指定，設計用於在等於或低於（優於）4.5 K (−268.65 °C) 的環境溫度下運作。 技術註解：就 3A901.a 而言，CMOS 積體電路也稱為低溫 CMOS 或低溫 CMOS。 b.參數訊號放大器具有以下所有特徵： b.1.設計用於在低於 1 K (−272.15 °C) 的環境溫度下運作； b.2.設計用於在 2 GHz 至 15 GHz	--	3A901 Electronic items, not specified by ECCN 3A001, as follows： a. Complementary Metal Oxide Semiconductor (CMOS) integrated circuits, not specified by 3A001.a.2, designed to operate at an ambient temperature equal to or less (better) than 4.5 K (−268.65 °C). Technical Note: For the purposes of 3A901.a, CMOS integrated circuits are also referred to as cryogenic CMOS or cryo-CMOS. b. Parametric signal amplifiers having all of the following: b.1. Designed for operation at an ambient temperature below 1 K (−272.15 °C); b.2. Designed for operation at any

修正條目	現行內容	擬修正/新增內容	現行內容英譯	擬修正/新增內容英譯
		（含）的任何頻率下運作；和 b.3.在 1 K (−272.15 °C) 下，從 2 GHz 到 15 GHz（包括 15 GHz）的任何頻率下，雜訊係數均小於（優於）0.015 dB。 註解： 就3A901.b而言，參數訊號放大器包含行波參數放大器（TWPA）。 技術註解： 就3A901.b而言，參數訊號放大器也可稱為量子限制放大器(QLA)。		frequency from 2 GHz up to and including 15 GHz; and b.3. A noise figure less (better) than 0.015 dB at any frequency from 2 GHz up to and including 15 GHz at 1 K (−272.15 °C). Note: For the purposes of 3A901.b, parametric signal amplifiers include Travelling Wave Parametric Amplifiers (TWPAs). Technical Note: For the purposes of 3A901.b, parametric signal amplifiers may also be referred to as Quantum-limited amplifiers (QLAs).
3A904	新增	3A904 低溫冷卻系統及零件如下： a.系統額定在 0.1 K (−273.05 °C) 或以下的溫度下提供大於或等於 600 µW 的冷卻功率，持續時間超過 48 小時； b.兩級脈衝管製冷機的額定溫度維持在 4 K (−269.15 °C) 以下，並在 4.2 K (−268.95 °C) 或以下時提供大於或等於 1.5 W 的冷卻功率。	--	3A904 Cryogenic cooling systems and components, as follows： a. Systems rated to provide a cooling power greater than or equal to 600 µW at or below a temperature of 0.1 K (−273.05 °C) for a period of greater than 48 hours; b. Two-stage pulse tube cryocoolers rated to maintain a temperature below 4 K (−269.15 °C) and provide a cooling power greater than or equal to 1.5 W at or below a temperature of 4.2 K (−268.95 °C).
3B001.a.2	2.設計用於以金屬進行化合物半導體磊晶之有機金屬化學氣相沉積(MOCVD)反應器，其有 2 個或以上下列元素：鋁、鎵、銦、砷、磷、銻或氮；	Addition of «oxygen» to compounds for equipment for epitaxial 設計用於以金屬進行化合物半導體磊晶之有機金屬化學氣相沉積(MOCVD)反應器，其有2個或以	2.Metal Organic Chemical Vapour Deposition (MOCVD) reactors designed for compound semicon-ductor epitaxial growth of material having two or more of the following elements: aluminium, gallium, indium, arsenic, phosphorus,	2.Metal Organic Chemical Vapour Deposition (MOCVD) reactors designed for compound semiconductor epitaxial growth of material having two or more of the following elements: aluminium, gallium, indium, arsenic, phosphorus, antimony, oxygen or

修正條目	現行內容	擬修正/新增內容	現行內容英譯	擬修正/新增內容英譯
		上下列元素：鋁、鎵、銦、砷、磷、銻、氧或氮；	antimony, or nitrogen;	nitrogen;
3B001.e 技術註解1	1.3B001.e.1.所述'半導體製程設備'，為提供半導體實體加工生產之模組工具，其具有不同功能，如沉積、植入或熱處理等。	1. 3B001.e.所述'半導體製程設備'，為提供半導體實體加工〝生產〞之模組工具，其具有不同功能，如沉積、植入或熱處理等。	1.For the purpose of 3B001.e.1., 'semiconductor process tools' refers to modular tools that provide physical processes for semiconductor production that are functionally different, such as deposition, implant or thermal processing.	1.For the purposes of 3B001.e.1., 'semiconductor process tools' refers to modular tools that provide physical processes for semiconductor "production" that are functionally different, such as deposition, implant or thermal processing.
3B001.q	新增	3B001 q.為積體電路設計的〝EUV〞光罩和〝EUV〞倍縮式光罩，未由3B001.g指定，並具有由3B001.j指定的光罩〝基板毛坯〞； 技術註解：就 3B001.q 而言，安裝有薄膜的光罩版或倍縮式光罩被視為光罩版和倍縮式光罩。	--	3B001 q. " EUV " masks and " EUV "reticles, designed for integrated circuits, not specified by 3B001.g, and having a mask " substrate blank "specified by 3B001.j; Technical Notes: For the purposes of 3B001.q, masks or reticles with a mounted pellicle are considered masks and reticles.
3B903	新增	3B903 掃描電子顯微鏡（SEM）設備，專為成像半導體設備或積體電路而設計，具下列所有特性： a.載物台放置精度小於（優於）30 nm； b.使用雷射干涉測量法進行載物台定位測量； c.基於雷射干涉儀長度測量的視場（FOV）內位置校準； d.擷取並儲存大於2 x 10 8 像素的影像； e.垂直和水平方向FOV重疊小於5%； f. FOV拼接重疊小於50 nm；和 g.加速電壓超過21 kV。	--	3B903 Scanning Electron Microscope (SEM) equipment designed for imaging semiconductor devices or integrated circuits. a. Stage placement accuracy less (better) than 30 nm; b. Stage positioning measurement performed using laser interferometry; c. Position calibration within a field-of-view (FOV) based on laser interferometer length-scale measurement; d. Collection and storage of images having more than 2 x 10 8 pixels; e. FOV overlap of less than 5 percent in vertical and horizontal directions; f. Stitching overlap of FOV less than 50 nm; and

修正條目	現行內容	擬修正/新增內容	現行內容英譯	擬修正/新增內容英譯
		註解1： 3B903 包括專為晶片設計恢復而設計的 SEM 設備。 註解2： 3B903 不適用於設計用於接受半導體設備和材料國際 (SEMI) 標準晶圓載體的 SEM 設備，例如 200 毫米或更大的前開口統一 Pod (FOUP)。		g. Accelerating voltage more than 21 kV. Note 1: 3B903 includes SEM equipment designed for chip design recovery. Note 2: 3B903 does not apply to SEM equipment designed to accept a Semiconductor Equipment and Materials International (SEMI) standard wafer carrier, such as a 200 mm or larger Front Opening Unified Pod (FOUP).
3B904	新增	3B904 低溫晶圓探測“設備”，具下列所有特性： a.設計用於在低於或等於 4.5 K (−268.65 °C) 的溫度下測試裝置；和 b.設計用於容納直徑大於或等於 100 毫米的晶圓。	--	3B904 Cryogenic wafer probing “equipment” , having all of the following： a. Designed to test devices at temperatures less than or equal to 4.5 K (−268.65 °C); and b. Designed to accommodate wafer diameters greater than or equal to 100 mm.
3C001 說明	新增	說明： 對於具有富含同位素的矽或鍺同位素層的材料，請參閱 3C907。	--	N.B.: For materials having layers of isotopically enriched Silicon or Germanium isotopes, see 3C907.
3C003	a.純度(金屬為基準)優於 99.999 %之鋁、鎵或銦之有機金屬化合物； b.純度(無機元素為基準) 優於 99.999 %之有機砷化物、有機銻化物、及有機磷化物。	a. 純度(金屬為基準)大於(優於) 99.999 %之鋁、鎵或銦之有機金屬化合物； b. 純度(無機元素為基準) 大於(優於) 99.999 %之有機砷化物、有機銻化物、及有機磷化物。	a.Organo-metallic compounds of aluminium, gallium or indium, having a purity (metal basis) better than 99,999 %; b.Organo-arsenic, organo-antimony and organo-phosphorus compounds, having a purity (inorganic element basis) better than 99,999 %.	a.Organo-metallic compounds of aluminium, gallium or indium, having a purity (metal basis) greater (better) than 99,999 %; b.Organo-arsenic, organo-antimony and organo-phosphorus compounds, having a purity (inorganic element basis) greater (better) than 99,999 %.

修正條目	現行內容	擬修正/新增內容	現行內容英譯	擬修正/新增內容英譯
3C004	純度優於 99.999 %之磷、砷、或銻之氫化物，包括被惰性氣體或氫氣稀釋者。	純度大於(優於) 99.999 %之磷、砷、或銻之氫化物，包括被惰性氣體或氫氣稀釋者。	Hydrides of phosphorus, arsenic or antimony, having a purity better than 99,999 %, even diluted in inert gases or hydrogen.	Hydrides of phosphorus, arsenic or antimony, having a purity greater (better) than 99,999 %, even diluted in inert gases or hydrogen.
3C907	新增	3C907具有至少一個以下任一外延生長層的「基板」組成的外延材料： a. 矽同位素雜質少於 0.08% 的矽同位素，而非矽-28 或矽-30；或 b. 鍺的同位素雜質少於 0.08%，但不包括鍺-70、鍺-72、鍺-74 或鍺-76。	--	3C907 Epitaxial materials consisting of a “substrate” having at least one epitaxially grown layer of any of the following： a. Silicon having an isotopic impurity less than 0.08% of silicon isotopes other than silicon-28 or silicon-30; or b. Germanium having an isotopic impurity less than 0.08% of germanium isotopes other than germanium-70, germanium-72, germanium-74, or germanium-76.
3C908	新增	3C908 含有下列物質的矽或鍺的氟化物、氫化物、氯化物： a. 矽同位素雜質少於 0.08% 的矽同位素，而非矽-28 或矽-30；或 b. 鍺的同位素雜質少於 0.08%，但不包括鍺-70、鍺-72、鍺-74 或鍺-76。	--	3C908 Fluorides, hydrides, chlorides, of silicon or germanium, containing any of the following a. Silicon having an isotopic impurity less than 0.08% of silicon isotopes other than silicon-28 or silicon-30; or b. Germanium having an isotopic impurity less than 0.08% of germanium isotopes other than germanium-70, germanium-72, germanium-74, or germanium-76.
3C909	新增	3C909 矽、氧化矽、鍺或氧化鍺，具下列任一特性： a. 矽同位素雜質少於 0.08% 的矽同位素，而非矽-28 或矽-30；或 b. 鍺的同位素雜質少於 0.08%，但不包括鍺-70、鍺-72、鍺-74 或鍺-76。 註解： 3C909 包括「基材」、塊、錠、	--	3C909 Silicon, silicon oxides, germanium or germanium oxides, containing any of the following a. Silicon having an isotopic impurity less than 0.08% of silicon isotopes other than silicon-28 or silicon-30; or b. Germanium having an isotopic impurity less than 0.08% of germanium isotopes other than germanium-70, germanium-72, germanium-74, or germanium-76.

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		晶錠和預製件。 說明： 對於具有富含同位素的矽 (Si) 或鍺 (Ge) 同位素層的材料，請參閱 3C907。		Note: 3C909 includes “substrates” , lumps, ingots, boules and preforms. N.B.: For materials having layers of isotopically enriched silicon (Si) or germanium (Ge) isotopes, see 3C907.
3D001	為〝開發〞或〝生產〞3A001.b.至3A002.h.或3B所述之設備而特別設計之〝軟體〞。	為〝開發〞或〝生產〞3A001.b.至3A002.h.或3B所述之設備而特別設計之〝軟體〞。	"Software" specially designed for the "development" or "production" of equipment specified in 3A001.b. to 3A002.h. or 3B.	"Software" specially designed for the "development" or "production" of equipment specified in 3A001.b. to 3A002.h. or 3B.
3D901	新增	未在其他地方指定，〝特別設計〞或修改用於管控 3A901.b、3B903 或 3B904 項目的〝開發〞或〝生產〞之〝軟體〞。	--	"Software", not specified elsewhere, ‘‘specially designed’’ or modified for the "development","production" of items controlled in 3A901.b, 3B903, or 3B904.
3D907	新增	〝軟體〞，設計用於從掃描電子顯微鏡（SEM）影像中提取〝GDSII〞或對應標準的佈局數據，並執行層對層分割，產生多層〝GDSII〞資料或電路網表。	--	"Software" designed to extract " GDSII " or equivalent standard layout data and perform layer-to- layer alignment from SEM images, and generate multi-layer " GDSII " data or the circuit netlist..
3E901	新增	〝技術〞，根據一般技術註解，用於 3A901、3A904、3B903、3B904、3C907、3C908 或 3C909 所控制項目的〝開發〞或〝生產〞。	--	"Technology" according to the General Technology Note for the "development" or "production" of items controlled by 3A901, 3A904, 3B903, 3B904, 3C907, 3C908, or 3C909.
3E905	新增	〝技術〞，根據一般技術註解，用於使用〝環繞閘極場效電晶體（GAAFET）〞建構的積體電路或設備的〝開發〞或〝生產〞。	--	"Technology" according to the General Technology Note for the "development" or "production" of integrated circuits or devices, using " Gate all-around Field-Effect Transistor " (" GAAFET ") structures.
4A906	新增	量子電腦及相關〝電子組件〞及〝零件〞： a.量子電腦，如下：	--	Quantum computers and related "electronic assemblies," and "components" therefor.

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		1.支援 34 個或更多但少於 100 個，'完全控制'、'連接'和'運作"物理量子位元'的量子電腦，且'C-NOT 錯誤'小於或等於 10−4； 2.支援 100 個或更多但少於 200 個，'完全控制'、'連接'和'運作"物理量子位元'的量子電腦，且'C-NOT 錯誤'小於或等於 10−3； 3.支援 200 個或更多但少於 350 個，'完全控制'、'連接'和'運作"物理量子位元'的量子電腦，且'C-NOT 錯誤'小於或等於 2 × 10−3； 4.支援 350 個或更多但少於 500 個，'完全控制'、'連接'和'運作"物理量子位元'的量子電腦，且'C-NOT 錯誤'小於或等於 3 × 10−3； 5.支援 500 個或更多但少於 700 個，'完全控制'、'連接'和'運作"物理量子位元'的量子電腦，且'C-NOT 錯誤'小於或等於 4 × 10−3； 6.支援 700 個或更多但少於 1,100 個，'完全控制'、'連接'和'運作"物理量子位元'的量子電腦，且'C-NOT 錯誤'小於或等於 5 × 10−3； 7.支援 1,100 個或更多但少於 2,000 個，'完全控制'、'連接'和'運作"物理量子位元'的量子電腦，且'C-NOT 錯誤'小於或等於 6 × 10−3； 8.支援 2000 個或更多'完全控制'、'連接'和'運作"物理量子位元'的量子電腦； b.為4A906.a規定的專案〝特別設計〞的量子位元設備和量子位元		a. Quantum computers, as follows: 1. Quantum computers supporting 34 or more, but fewer than 100, 'fully controlled', 'connected' and 'working' 'physical qubits', and having a 'C-NOT error' of less than or equal to 10−4; 2. Quantum computers supporting 100 or more, but fewer than 200, 'fully controlled', 'connected' and 'working' 'physical qubits', and having a 'C-NOT error' of less than or equal to 10−3; 3. Quantum computers supporting 200 or more, but fewer than 350, 'fully controlled', 'connected' and 'working' 'physical qubits', and having a 'C-NOT error' of less than or equal to 2 × 10−3; 4. Quantum computers supporting 350 or more, but fewer than 500, 'fully controlled', 'connected' and 'working' 'physical qubits', and having a 'C-NOT error' of less than or equal to 3 × 10−3; 5. Quantum computers supporting 500 or more, but fewer than 700, 'fully controlled', 'connected' and 'working' 'physical qubits', and having a 'C-NOT error' of less than or equal to 4 × 10−3; 6. Quantum computers supporting 700 or more, but fewer than 1,100, 'fully controlled', 'connected' and 'working' 'physical qubits', and having a 'C-NOT error' of less than or equal to 5 × 10−3; 7. Quantum computers supporting 1,100 or more, but fewer than 2,000, 'fully controlled', 'connected' and 'working' 'physical qubits', and having a 'C-NOT error' of less than or equal to 6 × 10−3; 8. Quantum computers supporting

修正條目	現行內容	擬修正/新增內容	現行內容英譯	擬修正/新增內容英譯
		電路； c.為4A906.a規定的專案〝特別設計〞的量子控制元件和量子測量裝置； 註解1： 4A906適用於電路模型（或基於閘的）和單向（或基於測量的）量子電腦。本項目不適用於絕熱（或退火）量子電腦。 註解2： 4A906 指定的項目不一定實際上包含任何量子位元。例如，基於光子方案的量子電腦不會永久包含可識別為量子位元的實體項目。相反，光子量子位元是在電腦運行時產生的，然後被丟棄。 註解3： 4A906.b 指定的項目包括半導體、超導和光子量子位元晶片和晶片陣列；表面離子阱陣列；其他量子位元限制技術；以及這些項目之間的連貫互連。 註解4： 4A906.c 適用於設計用於校準、初始化、操作或測量量子電腦的常駐量子位元的物品。 技術註解： 就 4A906 而言： 1.'物理量子位元'是一種兩級量子系統，用於透過未糾錯的操作和測量來表示量子邏輯的基本單位。'物理量子位元'與邏輯量子位元的差別在於，邏輯量子位元是		2,000 or more 'fully controlled', 'connected' and 'working' 'physical qubits'; b. Qubit devices and qubit circuits, containing or supporting arrays of 'physical qubits', and " specially designed " for items specified by 4A906.a; c. Quantum control components and quantum measurement devices, " specially designed " for items specified by 4A906.a; Note 1: 4A906 applies to circuit model (or gate-based) and one-way (or measurement-based) quantum computers. This entry does not apply to adiabatic (or annealing) quantum computers. Note 2: Items specified by 4A906 may not necessarily physically contain any qubits. For example, quantum computers based on photonic schemes do not permanently contain a physical item that can be identified as a qubit. Instead, the photonic qubits are generated while the computer is operating and then later discarded. Note 3: Items specified by 4A906.b include semiconductor, superconducting, and photonic qubit chips and chip arrays; surface ion trap arrays; other qubit confinement technologies; and coherent

修正條目	現行內容	擬修正/新增內容	現行內容英譯	擬修正/新增內容英譯
		由許多'物理量子位元'組成的糾錯量子位元。 2.'完全控制'意味著'物理量子位元'可以根據需要進行校準、初始化、閘控和讀出。 3.'連接'意味著可以在任意一對可用'運作"物理量子位元'之間執行雙量子位元閘操作。這並不一定需要全面的連結。 4.'運作'是指'物理量子位元'依據量子位元操作保真度的系統規格執行通用量子計算工作。 5.支援34個或更多'完全控制'、'連接'、'運作"物理量子位元'是指量子電腦限制、控制、測量和處理34個或更多'物理量子位元'所體現的量子資訊的能力。 6.'C-NOT 錯誤'是最近鄰的兩個'物理量子位元'受控非 (C-NOT) 閘的平均物理閘錯誤。		interconnects between such items. Note 4: 4A906.c applies to items designed for calibrating, initializing, manipulating or measuring the resident qubits of a quantum computer. Technical Notes: For the purposes of 4A906: 1. A 'physical qubit' is a two-level quantum system used to represent the elementary unit of quantum logic by means of manipulations and measurements that are not error corrected. 'Physical qubits' are distinguished from logical qubits, in that logical qubits are error-corrected qubits comprised of many 'physical qubits'. 2. 'Fully controlled' means the 'physical qubit' can be calibrated, initialized, gated, and read out, as necessary. 3. 'Connected' means that two-qubit gate operations can be performed between any arbitrary pair of the available 'working' 'physical qubits'. This does not necessarily entail all-to-all connectivity. 4. 'Working' means that the 'physical qubit' performs universal quantum computational work according to the system specifications for qubit operational fidelity.

修正條目	現行內容	擬修正/新增內容	現行內容英譯	擬修正/新增內容英譯
				5. Supporting 34 or more 'fully controlled', 'connected', 'working' 'physical qubits' refers to the capability of a quantum computer to confine, control, measure and process the quantum information embodied in 34 or more 'physical qubits'. 6. 'C-NOT error' is the average physical gate error for the nearest-neighbor two-'physical qubit' Controlled-NOT (C-NOT) gates.
4D906	新增	特別設計或修改用於〝開發〞或〝生產〞4A906.b 或 4A906.c 管控的商品的〝軟體〞。	--	"Software" "specially designed" or modified for the "development" or "production" of commodities controlled by 4A906.b or 4A906.c.
4E906	新增	〝技術〞依照一般技術註解，如下： a.用於〝開發〞或〝生產〞4A906.b、4A906.c 或 4D906 管控商品的〝技術〞； b. 〝使用〞4D906 管控〝軟體〞的〝技術〞。	--	"Technology" according to the General Technology Note as follows a. "Technology" for the "development" or "production" of items controlled by 4A906.b, 4A906.c, or 4D906; b. "Technology" for "use" of "software" controlled by 4D906.
5A001.b.2.b	b.合併一線性功率放大器結構，在以下條件，可同時支援多重訊號：頻率範圍 1.5 MHz 或以上，但小於 30 MHz，輸出功率1 kW 或以上時；或當頻率範圍 30 MHz 或以上，但不超過 87.5MHz，輸出功率 250 W 或以上時，以上〝瞬時頻寬〞超過一個倍頻或以上，且輸出諧波與失真度優於- 80 dB；	合併一線性功率放大器結構，在以下條件，可同時支援多重訊號：頻率範圍1.5 MHz或以上，但小於30 MHz，輸出功率1 kW或以上時；或當頻率範圍30 MHz或以上，但不超過87.5 MHz，輸出功率250 W或以上時，以上〝瞬時頻寬〞超過一個倍頻或以上，且輸出諧波與失真度小於(優於)- 80 dB；	b.Incorporating a linear power amplifier configuration having a capability to support multiple signals simultaneously at an output power of 1 kW or more in the frequency range of 1,5 MHz or more but less than 30 MHz, or 250 W or more in the frequency range of 30 MHz or more but not exceeding 87,5 MHz, over an "instantaneous bandwidth" of one octave or more and with an output harmonic and distortion content of better than -80 dB;	b.Incorporating a linear power amplifier configuration having a capability to support multiple signals simul taneously at an output power of 1 kW or more in the frequency range of 1,5 MHz or more but less than 30 MHz, or 250 W or more in the frequency range of 30 MHz or more but not exceeding 87,5 MHz, over an "instantaneous bandwidth" of one octave or more and with an output harmonic and distortion content of less(better) than -80 dB;

修正條目	現行內容	擬修正/新增內容	現行內容英譯	擬修正/新增內容英譯
5A101 註解	5A101 不管制下列各項： a.為載人航空器或衛星而設計或修改之設備； b.為陸地或海洋用途而設計或修改之地面設備； c.為商業、民間或'生命安全'(如資料完整性、飛航安全)之 GNSS 服務而設計之設備；	5A101不管制下列各項： a. 為載人航空器或衛星而設計或修改之設備； b. 為陸地或海洋用途而設計或修改之地面設備； c. 為商業、民間或'生命安全'(如資料完整性、飛航安全)之導航衛星系統服務而設計之設備；	5A101 does not control: a.Equipment designed or modified for manned aircraft or satellites; b.Ground based equipment designed or modified for terrestrial or marine applications; c.Equipment designed for commercial, civil or 'Safety of Life' (e.g. data integrity, flight safety) GNSS services;	5A101 does not control: a.Equipment designed or modified for manned aircraft or satellites; b.Ground based equipment designed or modified for terrestrial or marine applications; c.Equipment designed for commercial, civil or 'Safety of Life' (e.g. data integrity, flight safety) navigation satellite systems services;
5D001.e	e.5D001.a.或 5D001.c.所述之外，特別設計或修改用於執法部門監視或分析之〝軟體〞，提供下列所有者：	e. 5D001. a. 或5D001. c. 所述之外，特別設計或修改用於執法目的的監視或分析之〝軟體〞，提供下列所有者：	e."Software", other than that specified in 5D001.a. or 5D001.c., specially designed or modified for monitoring or analysis by law enforcement, providing all of the following:	e."Software", other than that specified in 5D001.a. or 5D001.c., specially designed or modified for monitoring or analysis for law enforcement purposes, providing all of the following:
5D001.e.2	2.依據搜尋通訊內容或元資料或 5D001.e.1 所述之搜尋之結果，映射關係網路或追蹤個別目標的移動。	中文不變更	2.Mapping of the relational network or tracking the movement of targeted individuals based on the results of searches on content of communication or metadata or searches as described in 5D001.e.1.	2.Mapping of the relational network or tracking the movement or location of targeted individuals based on the results of searches on content of communication or metadata or searches as described in 5D001.e.1.
5A002.a	a.設計或修改用於具'描述安全演算法'之'資料機密性密碼學'，~~其密碼功能可經由安全〝密碼啟用〞之外之任何方式進行使用、已啟用或能夠啟用~~，如下：	a.設計或修改用於具'描述安全演算法'之'資料機密性密碼學'，如下：	a.Designed or modified to use 'cryptography for data confidentiality' having a 'described security algorithm', where that cryptographic capability is usable, has been activated, or can be activated by any means other than secure "cryptographic activation", as follows:	a.Designed or modified to use 'cryptography for data confiden tiality' having a 'described security algorithm', as follows:
5A002. a 技術註解 .g .h .i .j	g.支援 a.到 f.描述中任何功能之關鍵管理。	g. 僅實施已發布或商業加密標準的無線〝個人區域網路〞功能； h. 專為銀行使用或貨幣交易（包括票價或信用卡功能的收集和結算）設計且限於此的加密操作； i. 支援且限於上述a至h段所述功能和能力的密鑰管理；或	g.Key management in support of any function described in paragraph a. to f. above.	g.Wireless "personal area network" functionality imple menting only published or commercial cryptographic standards; h.Cryptographic operations specially designed for and limited to banking use or money transactions, including the collection and settlement of fares or credit functions; i.Key management in support of and limited

修正條目	現行內容	擬修正/新增內容	現行內容英譯	擬修正/新增內容英譯
說明		j. 未啟動或啟用的加密功能或能力，且僅能透過安全的〝加密啟動〞方式啟動或啟用。 說明：有關〝加密啟動令牌〞項目，參見5A002.b、5D002.b及5E002.b。		to functions and capabilities described in paragraph a. to h. above; or j.Cryptographic functions or capabilities that have not been activated or enabled, and can only be activated or enabled by means of secure "cryptographic acti vation". N.B. For 'cryptographic activation token' items, see 5A002.b., 5D002.b. and 5E002.b.
5A002.a 註解 2.b	b. 特別設計且限用於銀行業務或'貨幣交易'之密碼設備； 技術註解： 5A002.a.註解2. b.中之'貨幣交易'包括費用的收取與結算，或信貸功能。料。	b. 刪除；	b.Cryptographic equipment specially designed and limited for banking use or 'money transactions'; Technical Note: For the purposes of 5A002.a. Note b., 'money transactions' includes the collection and settlement of fares or credit functions.	b.Not used;
5A002.a 註解 2.e	e.民用之可攜式或行動是無線電電話與類似客戶無線設備，其僅使用公開或商業用密碼標準(除了反盜版功能可能未被公布)，且符合密碼學註解中 a.2.至 a.4. 項規定 (第 5 類第 2 部分註解 3)，其為指定之民用工業應用客製，而不影響其在未客製之前裝置之密碼功能；	e. 為民用設計的可攜式或行動無線電話及類似客戶端無線設備，經特定民用產業應用客製化，且符合以下所有特性： 1.非客製化的設備符合加密註解（第5類－第2部分中的註解3）的規定； 2.非客製化設備的「資料保密加密」具有「所述安全演算法」，不受客製化影響，並且僅實施已發布或商業的密碼標準；	e.Portable or mobile radiotelephones and similar client wireless devices for civil use, that implement only published or commercial cryptographic standards (except for anti-piracy functions, which may be non- published) and also meet the provisions of paragraphs a.2. to a.4. of the Cryptography Note (Note 3 in Category 5, Part 2), that have been customised for a specific civil industry application with features that do not affect the cryptographic functionality of these original non-customised devices;	e.Portable or mobile radiotelephones and similar client wireless devices, designed for civil use, that have been customised for a specific civil industry application meeting all of the following: 1.The non-customised devices satisfy the provisions of the Cryptography Note (Note 3 in Category 5 – Part 2); and 2.The 'cryptography for data confidentiality' having a 'described security algorithm' of the non-customised devices is not affected by the customisation, and implements only published or commercial cryptographic standards;
5A002.a 註解 2.f	f.項目之〝資訊安全〞功能僅限於無線〝個人區域網路〞的功能，僅能使用公開或商業密碼標準；	f. 刪除；	f.Items, where the "information security" functionality is limited to wireless "personal area network" functionality, implementing only published or	f.Not used;

修正條目	現行內容	擬修正/新增內容	現行內容英譯	擬修正/新增內容英譯
			commercial cryptographic standards; 1.Implement only published or commercial cryptographic standards; and 2.The cryptographic capability is limited to a nominal operating range not exceeding 30 metres according to the manufacturer's specifications, or not exceeding 100 metres according to the manufacturer's specifications for equipment that cannot interconnect with more than seven devices;	
5A002.a 註解 2.g	g.設計為民用之行動無線電存取網路(RAN)設備，同時符合密碼學註解之 a.2.至 a.4.(第 5 類第 2 部分註解 3)之條文，具有 RF 輸出功率限制為 0.1 W (20 dBm)或以下，及 16 戶或以下之同時上線用戶；	g.設計為民用之行動無線電存取網路(RAN)設備，同時符合密碼學註解之 a.2.至a.4.(第 5 類第 2 部分註解 3)之條文，具有RF輸出功率限制為 0.1 W (20 dBm)或以下，及 32 戶或以下之同時上線用戶；	g.Mobile telecommunications Radio Access Network (RAN) equipment designed for civil use, which also meet the provisions of paragraphs a.2. to a.4. of the Cryptography Note (Note 3 in Category 5, Part 2), having an RF output power limited to 0,1W (20 dBm) or less, and supporting 16 or fewer concurrent users.	g.Mobile telecommunications Radio Access Network (RAN) equipment designed for civil use, which also meet the provisions of paragraphs a.2. to a.4. of the Cryptography Note (Note 3 in Category 5, Part 2), having an RF output power limited to 0,1W (20 dBm) or less, and supporting 32 or fewer concurrent users;
6A001.a.1.d	d.設計作為水面艦艇或水底載具定位之聲學系統與配備，且具下列所有特性，以及為其特別設計之零件：	d. 設計作為水面艦艇或可潛水載具定位之聲學系統與配備，且具下列所有特性，以及為其特別設計之零件：	d.Acoustic systems and equipment, designed to determine the position of surface vessels or underwater vehicles and having all the following, and specially designed components therefor:	d.Acoustic systems and equipment, designed to determine the position of surface vessels or submersible vehicles and having all the following, and specially designed components therefor:
6A001.a.1.d 註解	6A001.a.1.d.包括： a.使用同調〝訊號處理〞的設備在 2 個或以上標幟與水面艦艇或水底載具內之水中聽音器單元之間；	6A001.a.1.d.包括： a. 使用同調〝訊號處理〞的設備在2個或以上標幟與水面艦艇或可潛水載具內之水中聽音器單元之間；	6A001.a.1.d. includes: a.Equipment using coherent "signal processing" between two or more beacons and the hydrophone unit carried by the surface vessel or underwater vehicle;	6A001.a.1.d. includes: a.Equipment using coherent "signal processing" between two or more beacons and the hydrophone unit carried by the surface vessel or submersible vehicle;
6A001.a.2.a.4	4.於任何深度且無加速補償下，'水中聽音器靈敏度'高於-180 dB；	4. 於任何深度且無加速補償下，'水中聽音器靈敏度'大於(優於) -180 dB；	4.A 'hydrophone sensitivity' better than -180 dB at any depth with no acceleration compensation;	4.A 'hydrophone sensitivity' greater (better) than -180 dB at any depth with no acceleration compensation;

修正條目	現行內容	擬修正/新增內容	現行內容英譯	擬修正/新增內容英譯
6A001.a.2.a.6	6.設計在水深超過 1,000 公尺下操作，'水中聽音器靈敏度'在 4 kHz 以下優於-230 dB；	6. 設計在水深超過1,000公尺下操作，'水中聽音器靈敏度'在4 kHz以下大於(優於) -230 dB；	6.Designed for operation at depths exceeding 1 000m and having a 'hydrophone sensitivity' better than –230dB below 4kHz;	6.Designed for operation at depths exceeding 1 000 m and having a 'hydrophone sensitivity' greater (better) than -230 dB below 4 kHz;
6A001.a.2.b 技術註解	b.拖曳式水中聽音器陣列，具有下列任一功能： 技術註解： 就 6A001.a.2.b.目的，水中聽音器陣列包由許多水中聽音器組成，其提供多個聲音輸出頻道。 1.水中聽音器群組間距小於 12.5 公尺，或可修改成小於 12.5公尺； 2.設計或'可修改'成使用於水深超過 35 公尺； 技術註解： 就 6A001.a.2.b.2.目的，在 6A001.a.2.b.1.和 2.中的'可修改'係指，容許線路或連接線變動的配置方式，以更改水中聽音器群組間距或操作之水深極限，這些配置方式包括：線路數目中有超過 10 %的備用線路，水中聽音器群組間距調整區塊或可調式內部水深極限裝置，或可控制一組以上之水中聽音器群組。 3.6A001.a.2.d.所述之艏向感測器； 4.縱向增強之排列管； 5.組合陣列之直徑小於 40 mm； 6.刪除； 7.6A001.a.2.a.所述之水中聽音器特	b.拖曳式水中聽音器陣列，具有下列任一功能： 技術註解： 就 6A001.a.2.b.目的，水中聽音器陣列包由許多水中聽音器組成，其提供多個聲音輸出頻道。 1.水中聽音器群組間距小於 12.5 公尺，或可修改成小於 12.5公尺； 2.設計或'可修改'成使用於水深超過 35 公尺； 3.6A001.a.2.d.所述之艏向感測器； 4.縱向增強之排列管； 5.組合陣列之直徑小於 40 mm； 6.刪除； 7.6A001.a.2.a.所述之水中聽音器特性；或 8.6A001.a.2.g.所述基於加速度計之水中聲學感測器。 技術註解： 就 6A001.a.2.b.目的，'可修改'係指，容許線路或連接線變動的配置方式，以更改水中聽音器群組間距或操作之水深極限，這些配置方式包括：線路數目中有超過 10 %的備用線路，水中聽音器群組間距調整區塊或可調式內部水深極限裝置，或可控制一組以上之水中聽音器群組。	b.Towed acoustic hydrophone arrays having any of the following: Technical Note: For the purposes of 6A001.a.2.b., hydrophone arrays consist of a number of hydrophones providing multiple acoustic output channels. 1.Hydrophone group spacing of less than 12,5 m or 'able to be modified' to have hydrophone group spacing of less than 12,5 m; 2.Designed or 'able to be modified' to operate at depths exceeding 35 m; Technical Note: For the purposes of 6A001.a.2.b.2., 'able to be modified' in 6A001.a.2.b.1. and 2. means having provisions to allow a change of the wiring or interconnections to alter hydrophone group spacing or operating depth limits. These provisions are: spare wiring exceeding 10 % of the number of wires, hydrophone group spacing adjustment blocks or internal depth limiting devices that are adjustable or that control more than one hydrophone group. 3.Heading sensors specified in 6A001.a.2.d.;	b.Towed acoustic hydrophone arrays having any of the following: Technical Note: For the purposes of 6A001.a.2.b., hydrophone arrays consist of a number of hydrophones providing multiple acoustic output channels. 1.Hydrophone group spacing of less than 12,5 m or 'able to be modified' to have hydrophone group spacing of less than 12,5 m; 2.Designed or 'able to be modified' to operate at depths exceeding 35 m; 3.Heading sensors specified in 6A001.a.2.d.; 4.Longitudinally reinforced array hoses; 5.An assembled array of less than 40 mm in diameter; 6.Not used; 7.Hydrophone characteristics specified in 6A001.a.2.a.; or 8.Accelerometer-based hydro-acoustic sensors specified in 6A001.a.2.g.;

修正條目	現行內容	擬修正/新增內容	現行內容英譯	擬修正/新增內容英譯
	性；或 8.6A001.a.2.g.所述基於加速度計之水中聲學感測器。		4.Longitudinally reinforced array hoses; 5.An assembled array of less than 40 mm in diameter; 6.Not used; 7.Hydrophone characteristics specified in 6A001.a.2.a.; or 8.Accelerometer-based hydro-acoustic sensors specified in 6A001.a.2.g.;	6A001a. 2. b. 8. Technical Note: For the purposes of 6A001.a.2.b., 'able to be modified' means having provisions to allow a change of the wiring or interconnections to alter hydrophone group spacing or operating depth limits. These provisions are: spare wiring exceeding 10 % of the number of wires, hydrophone group spacing adjustment blocks or internal depth limiting devices that are adjustable or that control more than one hydrophone group.
6A001.a.2.d.1	1.〝準確度〞優於 0.5°；及	1. 〝準確度〞小於(優於) 0.5°；及	1.An "accuracy" of better than 0,5°; and	1.An "accuracy" of less (better) than 0,5°; and
6A001.a.2.g.2	2.整體'加速度靈敏度'優於 48 dB(以 1,000 mV rms 每 1 g 為基準)；	2. 整體'加速度靈敏度'大於(優於) 48 dB(以1,000 mV rms每1 g為基準)	2.Having an overall 'acceleration sensitivity' better than 48 dB (reference 1 000 mV rms per 1g);	2.Having an overall 'acceleration sensitivity' greater (better) than 48 dB (reference 1 000 mV rms per 1g);
6A001.b.1.b	b.具有優於速度之 1 %的速度〝準確度(或稱〝精度〞)〞；	b. 具有小於 (優於)速度之1 %的速度〝準確度(或稱〝精度〞)〞；	b.Having speed "accuracy" better than 1 % of speed;	b.Having speed "accuracy" less (better) than 1 % of speed;
6A001.b.2	2.都卜勒聲納記錄設備具有優於速度之 1 %的速度〝準確度(或稱〝精度〞)〞；	2. 都卜勒聲納記錄設備具有小於 (優於)速度之1 %的速度〝準確度(或稱〝精度〞)〞；	2.Doppler-velocity sonar log equipment having speed "accuracy" better than 1 % of speed.	2.Doppler-velocity sonar log equipment having speed "accuracy" less (better) than 1 % of speed.
6A002.a.2 技術註解	技術註解： 就 6A002.a.2.目的，'電子倍增'為電子影像增強形式，定義為由碰撞電離子增益程序導致電子載體產生。'電子倍增'感測器可採取的形式為影像增強管、固態偵測器或〝焦面陣列〞。	刪除6A002.a.2技術註解	Technical Note: For the purposes of 6A002.a.2., 'charge multiplication' is a form of electronic image amplification and is defined as the generation of charge carriers as a result of an impact ionization gain process. 'Charge multiplication' sensors may take the form of an image intensifier tube,	--

修正條目	現行內容	擬修正/新增內容	現行內容英譯	擬修正/新增內容英譯
			solid state detector or "focal plane array".	
6A002.a.2.a.2.b	b.除微通道板外，為達'電子倍增'特別設計或改裝之電子感測裝置，其非合併像素間距為 500 μm 或以下；及	b.除微通道板外，為達〝電子倍增〞特別設計或改裝之電子感測裝置，其非合併像素間距為 500 μm或以下；及	b.An electron sensing device with a non-binned pixel pitch of 500 μm or less, specially designed or modified to achieve 'charge multiplication' other than by a microchannel plate; and	b.An electron sensing device with a non-binned pixel pitch of 500 μm or less, specially designed or modified to achieve "charge multiplication" other than by a microchannel plate; and
6A002.a.2.b.2.b	b.除微通道板外，為達'電子倍增'特別設計或改裝之電子感測裝置，其非合併像素間距為 500 μm 或以下；及	b. 除微通道板外，為達〝電子倍增〞特別設計或改裝之電子感測裝置，其非合併像素間距為500 μm或以下；及	b.An electron sensing device with a non-binned pixel pitch of 500 μm or less, specially designed or modified to achieve 'charge multiplication' other than by a microchannel plate; and	b.An electron sensing device with a non-binned pixel pitch of 500 μm or less, specially designed or modified to achieve "charge multiplication" other than by a microchannel plate; and
6A002.a.2.c.2	2. 除微通道板外，為達'電子倍增'特別設計或改裝之電子感測裝置，其非合併像素間距為 500 μm 或以下；	2. 除微通道板外，為達〝電子倍增〞特別設計或改裝之電子感測裝置，其非合併像素間距為500 μm或以下；	2.An electron sensing device with a non-binned pixel pitch of 500 μm or less, specially designed or modified to achieve 'charge multiplication' other than by a microchannel plate;	2.An electron sensing device with a non-binned pixel pitch of 500 μm or less, specially designed or modified to achieve "charge multiplication" other than by a microchannel plate;
6A002.a.3 註解 2 c	c.特別設計或改造之〝焦面陣列〞，為達'電子倍增'，且其設計極限為具最高〝輻射靈敏度〞10 mA/W 或以下，在波長超過 760 nm，具有下列所有特性：	c. 特別設計或改造之〝焦面陣列〞，為達〝電子倍增〞，且其設計極限為具最高〝輻射靈敏度〞10 mA/W或以下，在波長超過760 nm，具有下列所有特性：	c."Focal plane arrays" specially designed or modified to achieve 'charge multiplication' and limited by design to have a maximum "radiant sensitivity" of 10 mA/W or less for wavelengths exceeding 760 nm, having all of the following:	c."Focal plane arrays" specially designed or modified to achieve "charge multiplication" and limited by design to have a maximum "radiant sensitivity" of 10 mA/W or less for wavelengths exceeding 760 nm, having all of the following:
6A002.a.3 技術註解	技術註解： '電子倍增'為電子影像增強形式，定義為由碰撞電離子增益程序導致電子載體產生。'電子倍增'感測器可採取的形式為影像增強管、固態偵測器或〝焦面陣列〞。	刪除6A002.a.3 技術註解	Technical Note: 'Charge multiplication' is a form of electronic image amplification and is defined as the generation of charge carriers as a result of an impact ionization gain process. 'Charge multiplication' sensors may take the form of an image intensifier tube, solid state detector or "focal plane array".	--
6A002.a.3.a.2.b	b.特別設計或改裝為達'電子倍增'且最高〝輻射靈敏度〞超過 10	b. 特別設計或改裝為達〝電子倍增〞且最高〝輻射靈敏度〞超過 10 mA/W；	b.Specially designed or modified to achieve 'charge multiplication' and having a maximum "radiant	b.Specially designed or modified to achieve "charge multiplication" and having a maximum "radiant sensitivity"

修正條目	現行內容	擬修正/新增內容	現行內容英譯	擬修正/新增內容英譯
	mA/W；		sensitivity" exceeding 10 mA/W;	exceeding 10 mA/W;
6A002.a.3.b.2.b	b.特別設計或改裝為達'電子倍增'且最高〝輻射靈敏度〞超過 10 mA/W；	b. 特別設計或改裝為達〝電子倍增〞且最高〝輻射靈敏度〞超過 10 mA/W；	b.Specially designed or modified to achieve 'charge multiplication' and having a maximum "radiant sensitivity" exceeding 10 mA/W;	b.Specially designed or modified to achieve "charge multiplication" and having a maximum "radiant sensitivity" exceeding 10 mA/W;
6A002.b 註解	註解：6A002.b.1.不管制尖峰反應在波長範圍超過 300 nm，但不超過 900 nm 之〝單頻譜影像感應器〞，且只納入下列任一項非〝太空級〞偵測器或非〝太空級〞〝焦面陣列〞： 1.非為達'電子倍增'而設計或改裝之電荷耦合元件 (CCD)；或 2. 非為達'電子倍增'而設計或改裝之互補金屬氧化半導體(CMOS)元件。	註解：6A002.b.1.不管制尖峰反應在波長範圍超過300 nm，但不超過900 nm之〝單頻譜影像感應器〞，且只納入下列任一項非〝太空級〞偵測器或非〝太空級〞〝焦面陣列〞： 1. 非為達〝電子倍增〞而設計或改裝之電荷耦合元件(CCD)；或 2. 非為達〝電子倍增〞而設計或改裝之互補金屬氧化半導體(CMOS)元件。	Note: 6A002.b.1. does not control "monospectral imaging sensors" with a peak response in the wavelength range exceeding 300 nm but not exceeding 900 nm and only incorporating any of the following non–"space- qualified" detectors or non–"space-qualified" "focal plane arrays": Note: 1.Charge Coupled Devices (CCD) not designed or modified to achieve 'charge multiplication'; or 2.Complementary Metal Oxide Semiconductor (CMOS) devices not designed or modified to achieve 'charge multiplication'.	Note: 6A002.b.1. does not control "monospectral imaging sensors" with a peak response in the wavelength range exceeding 300 nm but not exceeding 900 nm and only incorporating any of the following non–"space- qualified" detectors or non–"space-qualified" "focal plane arrays": Note: 1.Charge Coupled Devices (CCD) not designed or modified to achieve "charge multiplication"; or 2.Complementary Metal Oxide Semiconductor (CMOS) devices not designed or modified to achieve "charge multiplication".
6A003.a.3	3.電子式高速掃描攝影機時間解析度優於 50 ns；	3. 電子式高速掃描攝影機時間解析度小於(優於)50 ns；	3.Electronic streak cameras having temporal resolution better than 50 ns;	3.Electronic streak cameras having temporal resolution less (better) than 50 ns;
6A005.f.3.a	a.波長大於 1 μm 時，其〝準確度(或稱〝精度〞)〞等於或小於 0.1μm；	a. 波長大於1 μm時，其〝準確度(或稱〝精度〞)〞等於或小於(優於) 0.1μm；	a.An "accuracy" of 0,1 μm or less, for wavelengths greater than 1 μm; or	a.An "accuracy" of 0,1 μm or less (better), for wavelengths greater than 1 μm; or
6A005.g.2	2.〝雷射〞頻率穩定度等於或優於(小於)10 MHz；	2. 〝雷射〞頻率穩定度等於或小於(優於)10 MHz；	2."Laser" frequency stability equal to or better (less) than 10 MHz;	2."Laser" frequency stability equal to or less (better) than 10 MHz;
6A005.g.4	4.光學系統解析度優於(小於)1 mm；及	4. 光學系統解析度小於(優於)1 mm；及	4.Optical system resolution better (less) than 1 nm; and	4.Optical system resolution less (better) than 1 nm; and
6A006.a.-c	〝磁力計〞及其子系統，如下： 1. 〝磁力計〞使用〝超導〞	〝磁力計〞及其子系統，如下： 1. 〝磁力計〞使用〝超導〞(SQUID)〝技術〞，且具下列任	a."Magnetometers" and subsystems as follows:	a."Magnetometers" and subsystems as follows:

修正條目	現行內容	擬修正/新增內容	現行內容英譯	擬修正/新增內容英譯
	(SQUID)〝技術〞，且具下列任一特性： a. 設計作為靜態操作之SQUID系統，於無特殊設計之消減行動雜訊子系統下，其〝靈敏度〞在每赫茲頻率下，等於或小於(優於)每平方根赫茲50 fT (rms)；或 b. SQUID系統行動磁力計之〝靈敏度〞在每赫茲頻率下，小於(優於)每平方根赫茲20 pT (rms)，且特別設計為消減行動雜訊； 2. 〝磁力計〞使用光學致動或核進動(質子/ Overhauser)〝技術〞，其〝靈敏度〞在每赫茲頻率下，小於(優於)每平方根赫茲20 pT(rms)； 3. 〝磁力計〞使用磁通閘〝技術〞，其〝靈敏度〞在每赫茲頻率下，小於(優於)每平方根赫茲10 pT (rms)； 4. 感應線圈式〝磁力計〞，其〝靈敏度〞小於(優於)下列任一者： a. 頻率小於1 Hz時，每平方根赫茲0.05 nT (rms)；	一特性： a. 設計作為靜態操作之SQUID系統，於無特殊設計之消減行動雜訊子系統下，其〝靈敏度〞在每赫茲頻率下，等於或小於(優於)每平方根赫茲50 fT (rms)；或 b. SQUID系統行動磁力計之〝靈敏度〞在每赫茲頻率下，小於(優於)每平方根赫茲20 pT (rms)，且特別設計為消減行動雜訊； 2. 〝磁力計〞使用光學致動或核進動(質子/ Overhauser)〝技術〞，其〝靈敏度〞在每赫茲頻率下，小於(優於)每平方根赫茲20 pT(rms)； 3. 〝磁力計〞使用磁通閘〝技術〞，其〝靈敏度〞在每赫茲頻率下，小於(優於)每平方根赫茲10 pT (rms)； 4. 感應線圈式〝磁力計〞，其〝靈敏度〞小於(優於)下列任一者： a. 頻率小於1 Hz時，每平方根赫茲0.05 nT (rms)； b. 頻率為1 Hz或以上，但不超過10 Hz，每平方根赫茲1×10-3 nT (rms)；或 c. 頻率超過10 Hz時，每平方根	1."Magnetometers" using "superconductive" (SQUID) "technology" and having any of the following: a.SQUID systems designed for stationary operation, without specially designed subsystems designed to reduce in-motion noise, and having a 'sensitivity' equal to or lower (better) than 50 fT (rms) per square root Hz at a frequency of 1 Hz; or b.SQUID systems having an in-motion-magnetometer 'sensitivity' lower (better) than 20 pT (rms) per square root Hz at a frequency of 1 Hz and specially designed to reduce in-motion noise; 2."Magnetometers" using optically pumped or nuclear precession (proton/Overhauser) "technology" having a 'sensitivity' lower (better) than 20 pT (rms) per square root Hz at a frequency of 1 Hz; 3."Magnetometers" using fluxgate "technology" having a 'sensitivity' equal to or lower (better) than 10 pT (rms) per square root Hz at a frequency of 1 Hz; 4.Induction coil "magnetometers" having a 'sensitivity' lower (better) than any of the following: a.0,05 nT (rms) per square root Hz at frequencies of less than 1 Hz;	1."Magnetometers" using "superconductive" (SQUID) "technology" and having any of the following: a.SQUID systems designed for stationary operation, without specially designed subsystems designed to reduce in-motion noise, and having a 'sensitivity' equal to or less (better) than 50 fT (rms) per square root Hz at a frequency of 1 Hz; or b.SQUID systems having an in-motion-magnetometer 'sensitivity' less (better) than 20 pT (rms) per square root Hz at a frequency of 1 Hz and specially designed to reduce in-motion noise; 2."Magnetometers" using optically pumped or nuclear precession (proton/Overhauser) "technology" having a 'sensitivity' less (better) than 20 pT (rms) per square root Hz at a frequency of 1 Hz; 3."Magnetometers" using fluxgate "technology" having a 'sensitivity' equal to or less (better) than 10 pT (rms) per square root Hz at a frequency of 1 Hz; 4.Induction coil "magnetometers" having a 'sensitivity' less (better) than any of the following: a.0,05 nT (rms) per square root Hz at frequencies of less than 1 Hz; b.1 × 10–3 nT (rms) per square root Hz

修正條目	現行內容	擬修正/新增內容	現行內容英譯	擬修正/新增內容英譯
	b. 頻率為1 Hz 或以上，但不超過10 Hz，每平方根赫茲1×10-3 nT (rms)；或 c. 頻率超過10 Hz 時，每平方根赫茲1×10-4 nT (rms)； 5. 光纖〝磁力計〞之〝靈敏度〞低於(優於)每平方根赫茲1 nT (rms)； b. 水下電場感測器，其〝靈敏度〞在1 Hz 測量時，小於(優於)每公尺每平方根赫茲 8 nanovolt。 c. 〝磁梯度計〞，如下： 1. 使用多個6A006.a.所述〝磁力計〞之〝磁梯度計〞； 2. 光纖〝固有磁梯度計〞，其磁場梯度之〝靈敏度〞低於(優於)每平方根赫茲0.3 nT/m rms； 3. 使用光纖技術以外〝技術〞之〝固有磁梯度計〞，其磁場梯度之〝靈敏度〞低於(優於)每平方根赫茲0.015 nT/m rms；	赫茲1×10-4 nT (rms)； 5. 光纖〝磁力計〞之〝靈敏度〞小於(優於)每平方根赫茲1 nT (rms)； b. 水下電場感測器，其〝靈敏度〞在1 Hz測量時，小於(優於)每公尺每平方根赫茲 8 nanovolt。 c. 〝磁梯度計〞，如下： 1. 使用多個6A006.a.所述〝磁力計〞之〝磁梯度計〞； 2. 光纖〝固有磁梯度計〞，其磁場梯度之〝靈敏度〞小於(優於)每平方根赫茲0.3 nT/m rms； 3. 使用光纖技術以外〝技術〞之〝固有磁梯度計〞，其磁場梯度之〝靈敏度〞小於(優於)每平方根赫茲0.015 nT/m rms；	b.1 × 10–3 nT (rms) per square root Hz at frequencies of 1 Hz or more but not exceeding 10 Hz; or c.1 × 10–4 nT (rms) per square root Hz at frequencies exceeding 10 Hz; 5.Fibre optic "magnetometers" having a 'sensitivity' lower (better) than 1 nT (rms) per square root Hz; b.Underwater electric field sensors having a 'sensitivity' lower (better) than 8 nanovolt per metre per square root Hz when measured at 1 Hz; c."Magnetic gradiometers" as follows: 1."Magnetic gradiometers" using multiple "magnetometers" specified in 6A006.a.; 2.Fibre optic "intrinsic magnetic gradiometers" having a magnetic gradient field 'sensitivity' lower (better) than 0,3 nT/m rms per square root Hz; 3."Intrinsic magnetic gradiometers", using "technology" other than fibre-optic "technology", having a magnetic gradient field 'sensitivity' lower (better) than 0,015 nT/m rms per square root Hz;	at frequencies of 1 Hz or more but not exceeding 10 Hz; or c.1 × 10–4 nT (rms) per square root Hz at frequencies exceeding 10 Hz; 5.Fibre optic "magnetometers" having a 'sensitivity' less (better) than 1 nT (rms) per square root Hz; b.Underwater electric field sensors having a 'sensitivity' less (better) than 8 nanovolt per metre per square root Hz when measured at 1 Hz; c."Magnetic gradiometers" as follows: 1."Magnetic gradiometers" using multiple "magnetometers" specified in 6A006.a.; 2.Fibre optic "intrinsic magnetic gradiometers" having a magnetic gradient field 'sensitivity' less (better) than 0,3 nT/m rms per square root Hz; 3."Intrinsic magnetic gradiometers", using "technology" other than fibre-optic "technology", having a magnetic gradient field 'sensitivity' less (better) than 0,015 nT/m rms per square root Hz;
6B004.a	a.測量絕對反射度之設備，其〝準確度(或稱〝精度〞)〞為反射值的0.1 %或更優者；	a. 測量絕對反射度之設備，其〝準確度(或稱〝精度〞)〞為反射值的小於(優於) 0.1 %；	a.Equipment for measuring absolute reflectance to an "accuracy" of equal to or better than 0,1 % of the reflectance value;	a.Equipment for measuring absolute reflectance to an "accuracy" of equal to or less (better) than 0,1 % of the reflectance value;

修正條目	現行內容	擬修正/新增內容	現行內容英譯	擬修正/新增內容英譯
6C005.b.2 技術註解	技術註解： 1.就6C005目的，核心之'數值孔徑'('NA')以光纖的發射波長量測。 2. 6C005.b.包括光纖有裝配端帽者。	註解： 6C005.b.包括光纖有裝配端帽者。 技術註解： 就6C005目的，核心之'數值孔徑'('NA')以光纖的發射波長量測。	Technical Notes: 1.For the purposes of 6C005.b.1.b., the core 'Numerical Aperture' ('NA') is measured at the emission wave-lengths of the fibre. 2.6C005.b. includes fibres assembled with end caps.	Note: 6C005.b. includes fibres assembled with end caps. Technical Note: For the purposes of 6C005.b., the core 'Numerical Aperture' ('NA') is measured at the emission wavelengths of the fibre.
6E003.a.2	2. 光學製造〝技術〞，用單點鑽石旋轉技術，在超過 0.5 m2 之非平面表面上，用單點鑽石旋轉技術，產生〝準確度〞優於 10 nm rms 的表面；	2. 光學製造〝技術〞，用單點鑽石旋轉技術，在超過0.5 m2之非平面表面上，用單點鑽石旋轉技術，產生〝準確度〞小於(優於)10 nm rms的表面；	2."Technology" for the fabrication of optics using single point diamond turning techniques to produce surface finish "accuracies" of better than 10 nm rms on non-planar surfaces exceeding 0,5 m2;	2."Technology" for the fabrication of optics using single point diamond turning techniques to produce surface finish "accuracies" of less (better) than 10 nm rms on non-planar surfaces exceeding 0,5 m2;
7A 說明	說明：水下載具之自動駕駛，參照第 8 類。雷達參照第 6 類。	說明：可潛水載具之自動駕駛，參照第8類。雷達參照第6類。	N.B For automatic pilots for underwater vehicles, see Category 8. For radar, see Category 6.	N.B. For automatic pilots for submersible vehicles, see Category 8. For radar, see Category 6.
7A003.b 技術註解	技術註解： 在7A003.b.指一系統，其將'慣性測量設備或系統'及'位置輔助參考'建立於同一單元中(即嵌入式)以實現增進性能。	註解： 7A003.b.指其將'慣性測量設備或系統'及'位置輔助參考'建立於同一單元中(即嵌入式) 的系統，以實現增進性能。	Technical Note: For the purposes of 7A003.b., this entry refers to systems in which 'inertial measurement equipment or systems' and other independent 'positional aiding references' are built into a single unit (i.e., embedded) in order to achieve improved performance.	Note: 7A003.b. refers to systems in which 'inertial measurement equipment or systems' and other inde pendent 'positional aiding references' are built into a single unit (i.e., embedded) in order to achieve improved performance.
7A105 註解	註解：7A105.b.2.及 7A105.b.3.不管制為商業、民用或'人命安全'(例如資料完整性、飛行安全)用途之'衛星導航系統'服務而設計之設備。 技術註解： 7A105 中之'衛星導航系統'包括全球	註解： 1.7A105.b.2.及 7A105.b.3.不管制為商業、民用或'人命安全'(例如資料完整性、飛行安全)用途之'衛星導航系統'服務而設計之設備。 2.7A105 中之'衛星導航系統'包括全球衛星導航系統(GNSS，例如	Note: 7A105.b.2. and 7A105.b.3. do not control equipment designed for commercial, civil or 'Safety of Life' (e.g., data integrity, flight safety) 'navigation satellite system' services. Technical Note: In 7A105, 'navigation satellite system' includes Global Navigation Satellite	Note: 1. 7A105.b.2. and 7A105.b.3. do not control equipment designed for commercial, civil or Safety of Life (e.g., data integrity, flight safety) navigation satellite system services. 2.In 7A105, navigation satellite system include Global Navi gation Satellite

修正條目	現行內容	擬修正/新增內容	現行內容英譯	擬修正/新增內容英譯
	衛星導航系統(GNSS，例如 GPS、GLONASS、Galileo 或 BeiDou)與區域衛星導航系統(RNSS，例如 NavIC、QZSS)。	GPS、GLONASS、Galileo或BeiDou)與區域衛星導航系統(RNSS，例如NavIC、QZSS)。	Systems (GNSS; e.g. GPS, GLONASS, Galileo or BeiDou) and Regional Navigation Satellite Systems (RNSS; e.g. NavIC, QZSS).	Systems (GNSS; e.g., GPS, GLONASS, Galileo or BeiDou) and Regional Navigation Satellite Systems (RNSS; e.g., NavIC, QZSS).
8A002.a.4	技術註解： 就 8A002.a.4.目的，不因 8C001 所述輸出'複合泡材'仍在製程中未達最後零件形式，而不受管制。	技術註解刪除	Technical Note: For the purposes of 8A002.a.4., this entry should not be defeated by the export of 'syntactic foam' specified in 8C001 when an intermediate stage of manufacture has been performed and it is not yet in the final component form.;	--
8A002.d.1	1.特別設計或改裝用於遙控操作水下載具；或	1. 特別設計或改裝用於遙控操作可潛水載具；或	d.Underwater vision systems specially designed or modified for remote operation with an underwater vehicle, employing techniques to minimise the effects of back scatter and including range-gated illumi-nators or "laser" systems;	1.Specially designed or modified for remote operation with a submersible vehicle; and
8A002.o	o.推進器、動力傳輸系統、發電系統及噪音抑減系統，如下：	o. 推進器、動力傳輸系統、發電系統及噪音抑減系統及相關設備，如下：	o.Propellers, power transmission systems, power generation systems and noise reduction systems, as follows:	o.Propellers, power transmission systems, power generation systems and noise reduction systems and related equipment, as follows:
8A002.o.2.d	d.包含〝複合〞材料零件，能傳輸大於 2 MW 之動力傳輸軸系統；	d. 採用〝複合〞材料軸的電力傳輸系統，設計用於傳輸超過10兆瓦的功率；	d.Power transmission shaft systems incorporating "composite" material components and capable of transmitting more than 2 MW;	d.Power transmission systems incorporating "composite" shafts and designed to transmit power exceeding 10 MW;
8A002.o.3	3.設計用於排水量達 1,000 噸或以上船舶之噪音抑制系統，如下：	3. 設計用於排水量達1,000噸或以上船舶之噪音抑制系統及相關設備，如下：	3.Noise reduction systems designed for use on vessels of 1 000 tonnes displacement or more, as follows:	3.Noise reduction systems and related equipment, designed for use on vessels of 1 000 tonnes displacement or more, as follows:
9A006.a	a.特別設計用於太空載具，能限制低溫流體損耗每年低於 30 %之低溫冷凍機、飛行用真空瓶(杜爾瓶)、低溫	a. 設計用於能限制低溫流體損耗每年低於30 %之低溫冷凍機、飛行用真空瓶(杜爾瓶)、低溫熱管或低溫系統；	a.Cryogenic refrigerators, flightweight dewars, cryogenic heat pipes or cryogenic systems, specially designed for use in space vehicles and capable of restricting cryogenic fluid	a.Cryogenic refrigerators, flightweight dewars, cryogenic heat pipes or cryogenic systems, designed to restrict cryogenic fluid losses to less than 30 % per year;

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	熱管或低溫系統；		losses to less than 30 % per year;	
9A006.b	b.低溫容器或封閉迴路冷凍系統能提供 100 K (-173 °C)或以下溫度予持續飛行速度超過 3 馬赫之〝航空器〞、發射載具或〝太空載具〞；	b. 低溫容器或封閉循環冷凍系統，設計用於維持或產生低於或等於 100 K（-173.15°C）的溫度。	b.Cryogenic containers or closed-cycle refrigeration systems, capable of providing temperatures of 100 K (– 173 °C) or less for "aircraft" capable of sustained flight at speeds exceeding Mach 3, launch vehicles or "spacecraft";	b.Cryogenic containers or closed-cycle refrigeration systems, designed to maintain or produce temperatures less than or equal to 100 K (– 173,15 °C);
9A108.a 說明, 註解	新增	說明： 對於散裝或片狀絕緣材料，另請參閱 9C108。 註解： 在9A108中，應用於火箭發動機組件的絕緣材料（即外殼、噴嘴入口、外殼封蓋），包括含有絕緣或耐火材料的固化或半固化複合橡膠組件，這些組件為薄片材料形式。該絕緣材料亦可作為應力釋放套或襟翼被納入。	--	N.B. For insulation material in bulk or sheet form, SEE ALSO 9C108. Note: In 9A108, insulation intended to be applied to the components of a rocket motor, i.e. the case, nozzle inlets, case closures, includes cured or semi-cured compounded rubber components comprising sheet stock containing an insulating or refractory material. It may also be incorporated as stress relief boots or flaps.
9A121 技術註解	技術註解： 9A121 所述之節間連接器，尚包含安裝於〝飛彈〞、太空發射載具或探空火箭及其發射酬載裝置之間者。	註解： 在9A121中，節間電連接器亦包括安裝於〝飛彈〞、太空發射載具或探空火箭與其酬載之間的電連接器。	Technical Note: Interstage connectors referred to in 9A121 also include electrical connectors installed between the "missile", space launch vehicle or sounding rocket and their payload.	Note: In 9A121, interstage electrical connectors also include electrical connectors installed between the "missile", space launch vehicle or sounding rocket and their payload.
9B009 註解	說明：9B009 不管制生產粉末之工具。	註解：9B009不管制〝生產〞粉末之工具。	Note: 9B009 does not control tooling for the production of powder.	Note: 9B009 does not control tooling for the "production" of powder.
9B010	為生產 9A012 所述項目而特別設計之設備。	為〝生產〞9A012所述項目而特別設計之設備。	Equipment specially designed for the production of items specified in 9A012.	Equipment specially designed for the "production" of items specified in 9A012.
9B105 註解	註解： 9B105 不管制速度 3 馬赫或以下之風洞，其'測試段尺寸'等於或小於	註解： 1. 9B105所述之'空氣動力測試設施'包括風洞與震波風洞，用於氣流通過物體之研究。	Note: 9B105 does not control wind-tunnels for speeds of Mach 3 or less with dimension of the 'test cross section size' equal to or less than 250	Notes: 1.9B105 includes wind tunnels and shock tunnels for the study of airflow over objects.

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	250 mm。 技術註解： 1.9B105 所述之'空氣動力測試設施'包括風洞與震波風洞，用於氣流通過物體之研究。 2.9B105 註解所述之'測試段尺寸'指'測試段'之最大處，如圓形之直徑，或正方形之邊，或矩形之最長邊，或是橢圓形之主軸。 '測試段'為與氣流方向垂直之部分。 3.於 9B105 中，'飛彈'係指射程或航程超過 300 km 之完整火箭系統及無人飛行載具系統。	2.9B105不管制速度3馬赫或以下之風洞，其'測試段尺寸'等於或小於250 mm。 技術註解： 1. 9B105註解所述之'測試段尺寸'指'測試段'之最大處，如圓形之直徑，或正方形之邊，或矩形之最長邊，或是橢圓形之主軸。'測試段'為與氣流方向垂直之部分。 2. 於9B105中，'飛彈'係指射程或航程超過300 km之完整火箭系統及無人飛行載具系統。	mm. Technical Notes: 1.In 9B105 'aerodynamic test facilities' includes wind tunnels and shock tunnels for the study of airflow over objects. 2.In Note to 9B105, 'test cross section size' means the diameter of the circle, or the side of the square, or the longest side of the rectangle, or the major axis of the ellipse at the largest 'test cross section' location. 'Test cross section' is the section perpendicular to the flow direction. 3.In 9B105 'missile' means complete rocket systems and unmanned aerial vehicle systems capable of a range exceeding 300 km.	2.9B105 does not control wind-tunnels for speeds of Mach 3 or less with dimension of the 'test cross section size' equal to or less than 250 mm. Technical Notes: 1.In Note to 9B105, 'test cross section size' means the diameter of the circle, or the side of the square, or the longest side of the rectangle, or the major axis of the ellipse at the largest 'test cross section' location. 'Test cross section' is the section perpendicular to the flow direction. 2.In 9B105 'missile' means complete rocket systems and unmanned aerial vehicle systems capable of a range exceeding 300 km.
9B107 註解	技術註解： 1.'航空熱力學測試設施'包括電漿電弧噴射設施與電漿風洞，用於研究氣流對物件的熱和機械影響。 2.9B107 所述之'飛彈'係指射程或航程超過 300 km 之完整火箭系統及無人飛行載具系統。	註解： 1. 9B107包括電漿電弧噴射設施與電漿風洞，用於研究氣流對物件的熱和機械影響。 2. 9B107所述之'飛彈'係指射程或航程超過300 km之完整火箭系統及無人飛行載具系統。	Technical Notes: 1.'Aerothermodynamic test facilities' include plasma arc jet facilities and plasma wind tunnels for the study of thermal and mechanical effects of airflow on objects. 2.In 9B107 'missile' means complete rocket systems and unmanned aerial vehicle systems capable of a range exceeding 300 km.	Notes: 1.9B107 includes plasma arc jet facilities and plasma wind tunnels for the study of thermal and mechanical effects of airflow on objects. 2.In 9B107 'missile' means complete rocket systems and unmanned aerial vehicle systems capable of a range exceeding 300 km.
9C108 註解	新增	註解： 在9C108中，絕緣材料用於火箭發動機組件（如外殼、噴嘴入口、外殼封蓋），包括含有絕緣或耐火材料的固化或半固化橡膠片材。它也可能作為9A108中規定的	--	Note: In 9C108, insulation intended to be applied to the components of a rocket motor, i.e. the case, nozzle inlets, case closures, includes cured or semi-cured compounded rubber sheet stock containing an insulating or refractory

修正條目	現行內容	擬修正/新增內容	現行內容英譯	擬修正/新增內容英譯
		應力釋放套或襟翼被納入。		material. It may also be incorporated as stress relief boots or flaps specified in 9A108.
9D004.b 註解	註解： 9D004.b.不管制用於操作測試設施或操作者安全(例如超速停機、火災偵測與抑制)之軟體，或生產、維修或維護僅限於確認受測項目正確組裝或維修之軟體。	註解： 9D004.b.不管制用於操作測試設施或操作者安全(例如超速停機、火災偵測與抑制)之軟體，或〝生產〞、維修或維護僅限於確認受測項目正確組裝或維修之軟體。	9D004.b. does not control software for operation of the test facility or operator safety (e.g. overspeed shutdown, fire detection and suppression), or production, repair or maintenance acceptance-testing limited to determining if the item has been properly assembled or repaired.	9D004.b. does not control software for operation of the test facility or operator safety (e.g. overspeed shutdown, fire detection and suppression), or "production", repair or maintenance acceptance-testing limited to deter mining if the item has been properly assembled or repaired.
9E003.f	f.為〝生產〞特別設計用於高輸出柴油發動機之零件所〝必要〞之〝技術〞如下：	f. 為〝生產〞特別設計用於〝高功率柴油發動機〞之零件所〝必要〞之〝技術〞如下：	f."Technology" "required" for the "production" of specially designed components for high output diesel engines, as follows:	f."Technology" "required" for the "production" of specially designed components for "high output diesel engines", as follows:
9E003.g	g. 為〝開發〞或〝生產〞'高功率柴油發動機'所〝必要〞之〝技術〞，該發動機係以固態、氣相或液膜(或以前述各種組合)用於汽缸壁潤滑，容許操作溫度超過 723 K (450 °C)，溫度係於活塞頂環移行至最頂端之氣缸壁測得。	g. 為〝開發〞或〝生產〞〝高功率柴油發動機〞所〝必要〞之〝技術〞，該發動機係以固態、氣相或液膜(或以前述各種組合)用於汽缸壁潤滑，容許操作溫度超過723 K (450 °C)，溫度係於活塞頂環移行至最頂端之氣缸壁測得。	g."Technology" "required" for the "development" or "production" of 'high output diesel engines' for solid, gas phase or liquid film (or combinations thereof) cylinder wall lubrication and permitting operation to temperatures exceeding 723 K (450 °C), measured on the cylinder wall at the top limit of travel of the top ring of the piston;	g."Technology" "required" for the "development" or "production" of "high output diesel engines" for solid, gas phase or liquid film (or combinations thereof) cylinder wall lubrication and permitting operation to temperatures exceeding 723 K (450 °C), measured on the cylinder wall at the top limit of travel of the top ring of the piston;
9E003.g 技術註解	技術註解： '高功率柴油發動機'：若額定轉速為2,300 r.p.m.或以上，而轉速在2,300 r.p.m.時，其特定之制動平均有效壓力為1.8 MPa 或以上之柴油發動機。	(移至定義) 〝高功率柴油發動機〞(第9類)：若額定轉速為2,300 r.p.m.或以上，而轉速在2,300 r.p.m.時，其特定之制動平均有效壓力為1.8 MPa或以上之柴油發動機。	Technical Note: For the purposes of 9E003.g.,'high output diesel engines' are diesel engines with a specified brake mean effective pressure of 1,8 MPa or more at a speed of 2 300 r.p.m., provided the rated speed is 2 300 r.p.m. or more.	New Definition "High output diesel engines" (9) means diesel engines with a specified brake mean effective pressure of 1,8 MPa or more at a speed of 2 300 r.p.m., provided the rated speed is 2 300 r.p.m. or more.

第二項：一般軍用貨品清單修正對照表

修正條目	現行內容	擬修正/新增內容	現行內容英譯	擬修正/新增內容英譯
ML8 註解1 k.	k. N-吡咯酮；1-甲基-2-吡咯酮(CAS 872-50-4)；	k. 1-甲基-2-吡咯酮(N-甲基-2-吡咯酮)(CAS 872-50-4)；	k. N-pyrrolidinone; 1-methyl-2-pyrrolidinone (CAS 872-50-4);	k. 1-methyl-2-pyrrolidinone (N-methyl-2-pyrrolidinone) (CAS 872-50-4);
ML10. .g .j 註解1.c 註解2.a 註解3 註解4	為軍用而特別設計或改裝之〝航空器〞、〝比空氣輕載具〞、〝無人飛行載具〞(〝UAVs〞)、航空發動機及〝航空器〞設備、相關設備及零件，如下： g. 非屬 ML10.a.之機組人員生命維持設備、安全設備與其他緊急狀況逃離使用之裝置，其設計用於ML10.a.所述之〝航空器〞者；	為軍用而特別設計或改裝之〝航空器〞、〝比空氣輕載具〞、〝無人飛行載具〞(〝UAVs〞)、航空發動機、〝次軌道飛行器〞及〝航空器〞設備、相關設備及零件，如下： g. 非屬 ML10.a.之機組人員生命維持設備、安全設備與其他緊急狀況逃離使用之裝置，其設計用於 ML10.a.所述之〝航空器〞者或 ML10.j 所述的〝次軌道飛行器〞； j. 〝次軌道飛行器〞及相關設備，以及為其特別設計或改裝的零件，如下： 1.“次軌道飛行器”； 2. 發射設備、回收設備及地面支援設備； 3. 用於指揮或控制的設備。	ML10. "Aircraft", "lighter-than-air vehicles", "Unmanned Aerial Vehicles" ("UAVs"), aero-engines and "aircraft" equipment, related equipment, and components, as follows, specially designed or modified for military use: g. Aircrew life support equipment, aircrew safety equipment and other devices for emergency escape, not specified in ML10.a., designed for "aircraft" specified by ML10.a.;	ML10. "Aircraft", "lighter-than-air vehicles", "Unmanned Aerial Vehicles" ("UAVs"), aero-engines, "sub-orbital craft" and "aircraft" equipment, related equipment, and components, as follows, specially designed or modified for military use: g. Aircrew life support equipment, aircrew safety equipment and other devices for emergency escape, not specified in ML10.a., designed for "aircraft" specified by ML10.a. or "sub-orbital craft" specified in ML10.j.; j. "Sub-orbital craft" and related equipment, as follows, and specially designed or modified components therefor: 1."Sub-orbital craft"; 2.Launch equipment, recovery equipment and ground support equipment; 3.Equipment designed for command or

修正條目	現行內容	擬修正/新增內容	現行內容英譯	擬修正/新增內容英譯
				control.
	c. 已獲得1個或以上歐盟會員國或瓦聖那協議會員國之民航機構認證作為民用者。	c. 已獲得1個或以上瓦聖那協議會員國之民航機構認證作為民用者。	c. Certified for civil use by civil aviation authorities of one or more ~~EU Member States or~~ Wassenaar Arrangement Participating States.	c. Certified for civil use by civil aviation authorities of one or more Wassenaar Arrangement Participating States.
	a. 為軍用而設計或改裝之航空發動機，且已獲得1個或以上歐盟會員國或瓦聖那協議會員國之民航機構認證為〝民用航空器〞用途，或為其特別設計之零件；	a. 為軍用而設計或改裝之航空發動機，且已獲得1個或以上瓦聖那協議會員國之民航機構認證為〝民用航空器〞用途，或為其特別設計之零件；	a. Aero-engines designed or modified for military use which have been certified by civil aviation authorities of one or more ~~EU Member States or~~ Wassenaar Arrangement Participating States for use in "civil aircraft", or specially designed components therefor;	a. Aero-engines designed or modified for military use which have been certified by civil aviation authorities of one or more Wassenaar Arrangement Participating States for use in "civil aircraft", or specially designed components therefor;
	註解3：就 ML10.a. 及 ML10.d. 目的，為非軍用之〝航空器〞或改裝為軍用之航空發動機而特別設計之零件及相關設備，僅適用於作為軍事用途而需要改裝之軍用零件及軍用相關設備。	註解3：就 ML10.a.、ML10.d. 及 ML10.j. 目的，為非軍用之〝航空器〞或改裝為軍用之航空發動機或〝次軌道飛行器〞而特別設計之零件及相關設備，僅適用於作為軍事用途而需要改裝之軍用零件及軍用相關設備。	Note 3 For the purposes of ML10.a. and ML10.d., specially designed components and related equipment for non-military "aircraft" or aero-engines modified for military use applies only to those military components and to military related equipment required for the modification to military use.	Note 3 For the purposes of ML10.a., ML10.d. and ML10.j., specially designed components and related equipment for non-military "aircraft", aero-engines or "sub-orbital craft" modified for military use applies only to those military components and to military related equipment required for the modification to military use.
	註解4：就 ML10.a.目的，軍事用途包括：戰鬥、軍事偵察、突擊、軍事訓練、後勤補給、運輸及空投部隊或軍事設備。 註解5：ML10.a.不管制〝航空器〞或〝比空氣輕載具〞具下列所有特	註解4：就 ML10.a. 和 ML10.j. 目的，軍事用途包括：戰鬥、軍事偵察、突擊、軍事訓練、後勤補給、運輸及空投部隊或軍事設備。 註解5：ML10.a.不管制〝航空器〞或〝比空氣輕載具〞具下列所有特性：	Note 4 For the purposes of ML10.a., military use includes: combat, military reconnaissance, assault, military training, logistics support, and transporting and airdropping troops or military equipment.	Note 4 For the purposes of ML10.a. and ML10.j., military use includes: combat, military reconnaissance, assault, military training, logistics support, and transporting and

修正條目	現行內容	擬修正/新增內容	現行內容英譯	擬修正/新增內容英譯
	性： a.第一次生產於1946年之前； b.未包含一般軍用貨品清單管制之項目，除非該項目符合1個或以上~~歐盟會員國或~~瓦聖那協議會員國民航機構之安全與適航標準；及	a.第一次生產於1946年之前； b.未包含一般軍用貨品清單管制之項目，除非該項目符合1個或以上瓦聖那協議會員國民航機構之安全與適航標準；及	Note 5 ML10.a. does not apply to "aircraft" or "lighter-than-air-vehicles" that meet all of the following: a. Were first manufactured before 1946; b. Do not incorporate items specified by the Common Military List, unless the items are required to meet safety or airworthiness standards of civil aviation authorities of one or more ~~EU Member States or~~ Wassenaar Arrangement Participating States; and	airdropping troops or military equipment. Note 5 ML10.a. does not apply to "aircraft" or "lighter-than-air vehicles" that meet all of the following: a. Were first manufactured before 1946; b. Do not incorporate items specified by the Common Military List, unless the items are required to meet safety or airworthiness standards of civil aviation authorities of one or more Wassenaar Arrangement Participating States; and
ML18.註解	註解：ML18.a.及 ML18.b.包括下列設備： a. 連續式硝化器； b. 具下列任一特性之離心測試儀器或設備： 1. 由單個或多個總額定馬力大於298 kW(400 hp)之馬達驅動； 2. 酬載能力達113 kg 或以上；或 3. 酬載91 kg 或以上之離心加速能力達8 g 或以上； c. 壓榨脫水機(脫水壓機)； d. 特別設計或改裝為軍用〝炸藥〞	刪除註解	Note ML18.a. and ML18.b. include the following equipment: a. Continuous nitrators; b. Centrifugal testing apparatus or equipment having any of the following: 1. Driven by a motor or motors having a total rated horsepower of more than 298 kW (400 hp); 2. Capable of carrying a payload of	--

修正條目	現行內容	擬修正/新增內容	現行內容英譯	擬修正/新增內容英譯
	擠出成形之螺旋擠壓機； e. 將擠出之〝推進劑〞切成一定尺寸之切割機； f. 直徑1.85 m 或以上，生產能量逾227 kg 之顛動筒； g. 用於固體〝推進劑〞之連續式攪拌機； h. 用於軍用〝炸藥〞成分研磨之流體能研磨機； i. 能將 ML8.c.8.所述之金屬粉體做成均勻粒子球形之設備； j. 用於 ML8.c.3.所述之材料進行轉換之對流變換器。		113 kg or more; or 3. Capable of exerting a centrifugal acceleration of 8 g or more on a payload of 91 kg or more; c. Dehydration presses; d. Screw extruders specially designed or modified for military "explosive" extrusion; e. Cutting machines for the sizing of extruded "propellants"; f. Sweetie barrels (tumblers) 1,85 m or more in diameter and having over 227 kg product capacity; g. Continuous mixers for solid "propellants"; h. Fluid energy mills for grinding or milling the ingredients of military "explosives"; i. Equipment to achieve both sphericity and uniform particle size in metal powder listed in ML8.c.8.; j. Convection current converters for the conversion of materials listed in ML8.c.3.	

修正條目	現行內容	擬修正/新增內容	現行內容英譯	擬修正/新增內容英譯
ML19 .a .b .c 技術註解.(新增)	a. 為摧毀目標或迫使其任務中止而特別設計之'雷射'系統； b. 能摧毀目標或迫使其任務中止之粒子束系統； c. 能摧毀目標或迫使其任務中止之高功率射頻(RF)系統；	a. ML19.f.未列明的〝雷射〞'武器系統'； b. 粒子束'武器系統'； c. 高功率射頻(RF)'武器系統'； 技術註解： 就ML19.目的，'武器系統'的設計目的是損害、摧毀目標或導致目標任務中止。	a. "Laser" systems specially designed for destruction or effecting mission-abort of a target; b. Particle beam systems capable of destruction or effecting mission-abort of a target; c. High power Radio-Frequency (RF) systems capable of destruction or effecting mission-abort of a target;	a. "Laser" 'weapon systems' not specified by ML19.f.; b. Particle beam 'weapon systems'; c. High power Radio-Frequency (RF) 'weapon systems'; Technical Note For the purposes of ML19., 'weapon systems' are designed to damage, destroy or effect mission abort of a target.